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Spory

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(54) **METHOD FOR REMAPPING A PACKAGED EXTRACTED DIE**

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US 2018/0061724 A1 Mar. 1, 2018

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(63) Continuation-in-part of application No. 13/623,603, filed on Sep. 20, 2012, now abandoned, which is a (Continued)

(51) **Int. Cl.**
H01L 23/00 (2006.01)
H01L 23/10 (2006.01)
H01L 23/26 (2006.01)

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CPC **H01L 23/00** (2013.01); **H01L 24/03** (2013.01); **H01L 24/05** (2013.01); **H01L 24/48** (2013.01); **H01L 24/50** (2013.01); **H01L 24/92** (2013.01); **H01L 23/10** (2013.01); **H01L 23/26** (2013.01); **H01L 24/45** (2013.01); **H01L 24/85** (2013.01); **H01L 24/98** (2013.01); **H01L 2224/0381** (2013.01); **H01L 2224/0384** (2013.01);

(Continued)

(58) **Field of Classification Search**

CPC H01L 23/00; H01L 24/83; H01L 24/26
See application file for complete search history.

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Primary Examiner — Jae Lee

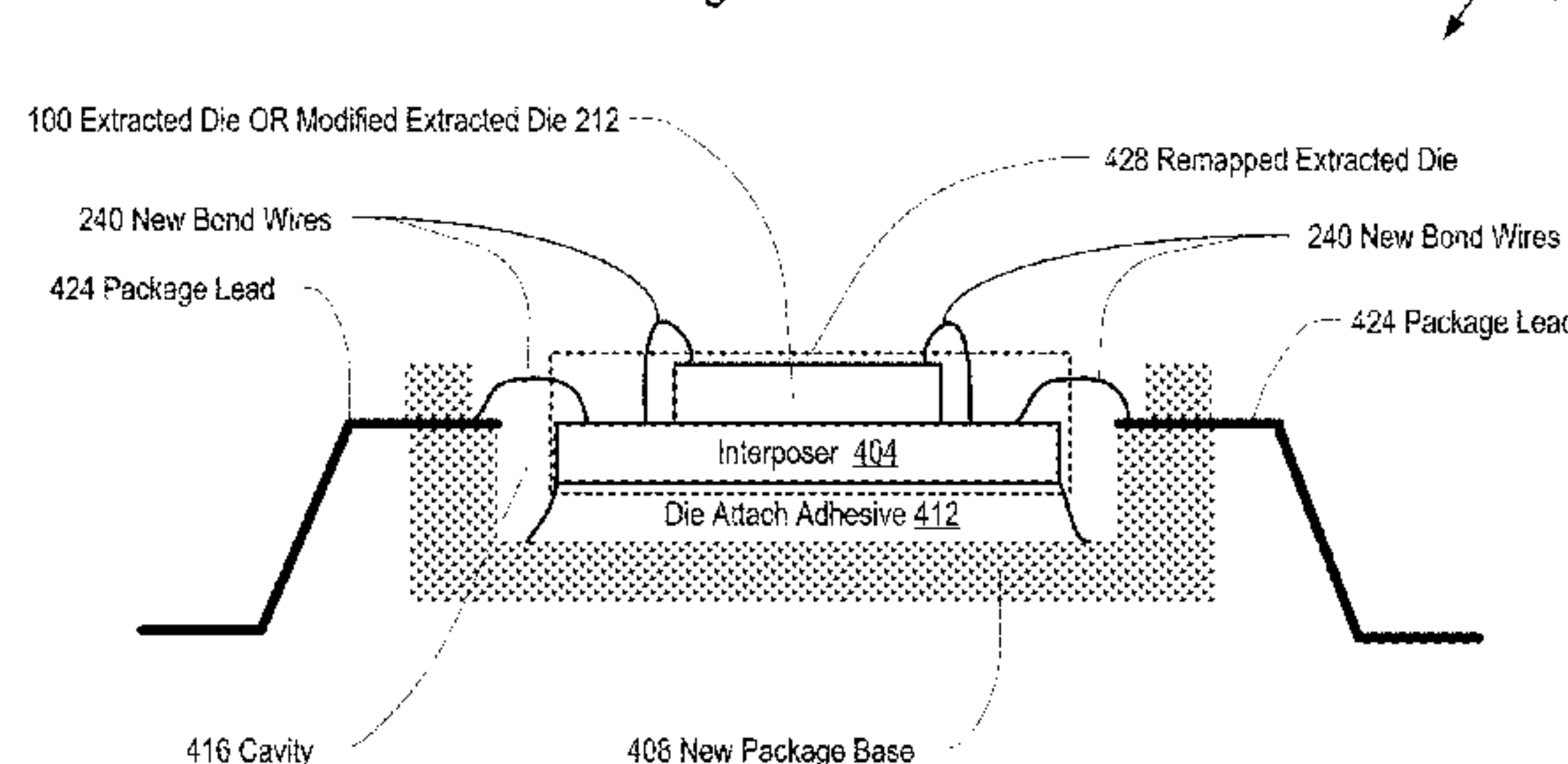
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(57) **ABSTRACT**

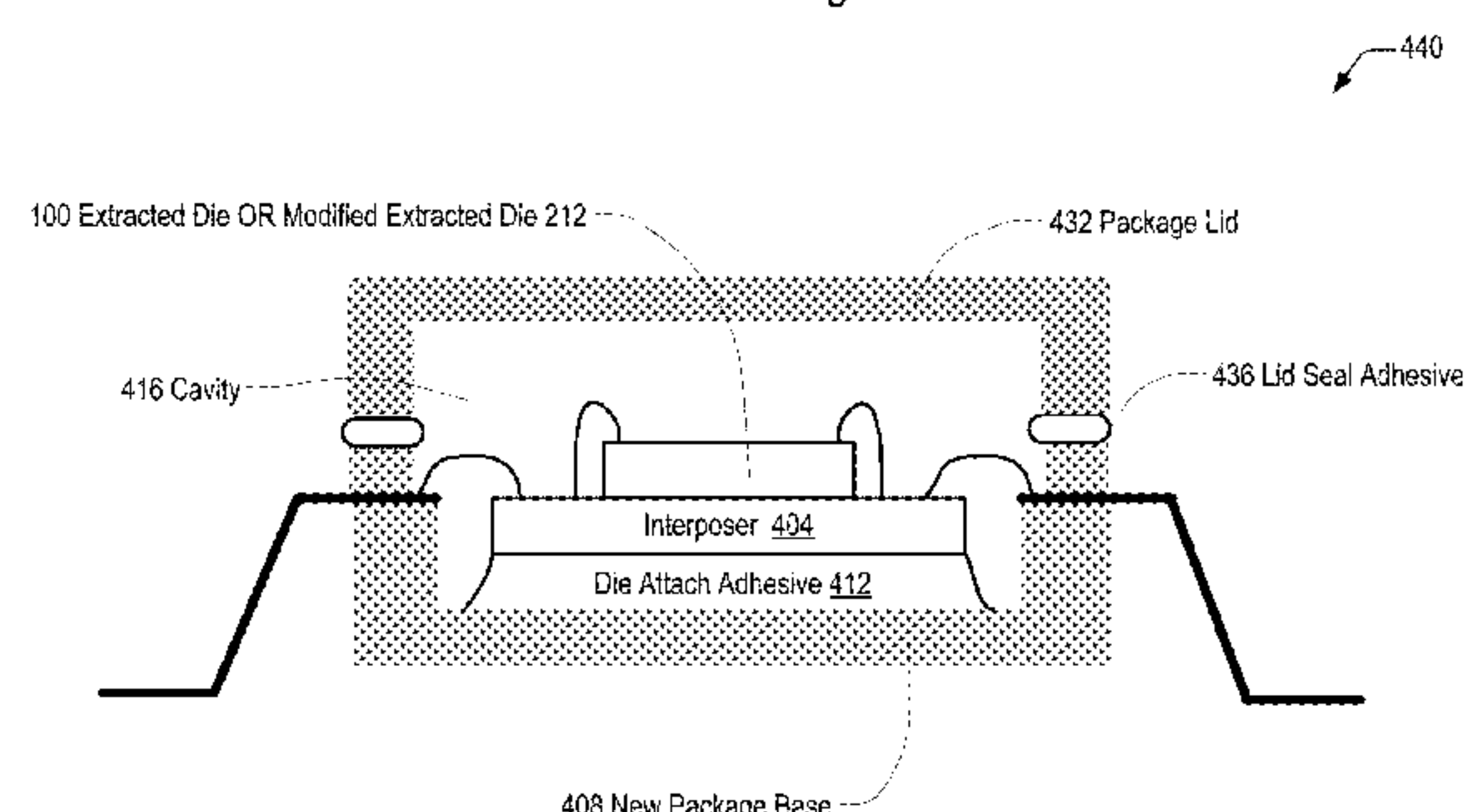
A method for remapping an extracted die is provided. The method includes one or more of removing an extracted die from a previous integrated circuit package, the extracted die including a plurality of original bond pads having locations that do not correspond to desired pin assignments of a new package base and bonding an interposer to the extracted die. The interposer includes first bond pads configured to receive new bond wires from the plurality of original bond pads and second bond pads corresponding to desired pin assignments of the new package base, each individually electrically coupled to one of the first bond pads and configured to receive new bond wires from package leads or downbonds of the new package base.

20 Claims, 14 Drawing Sheets

Assembled New Package Base With New Bond Wires



Assembled Non-Hermetic Package With Extracted Die



Related U.S. Application Data

continuation of application No. 13/283,293, filed on Oct. 27, 2011, now abandoned.

(52) U.S. Cl.

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Fig. 1 *Extracted Die with Original Bond Pads, Original Ball Bonds, and Original Bond Wires*

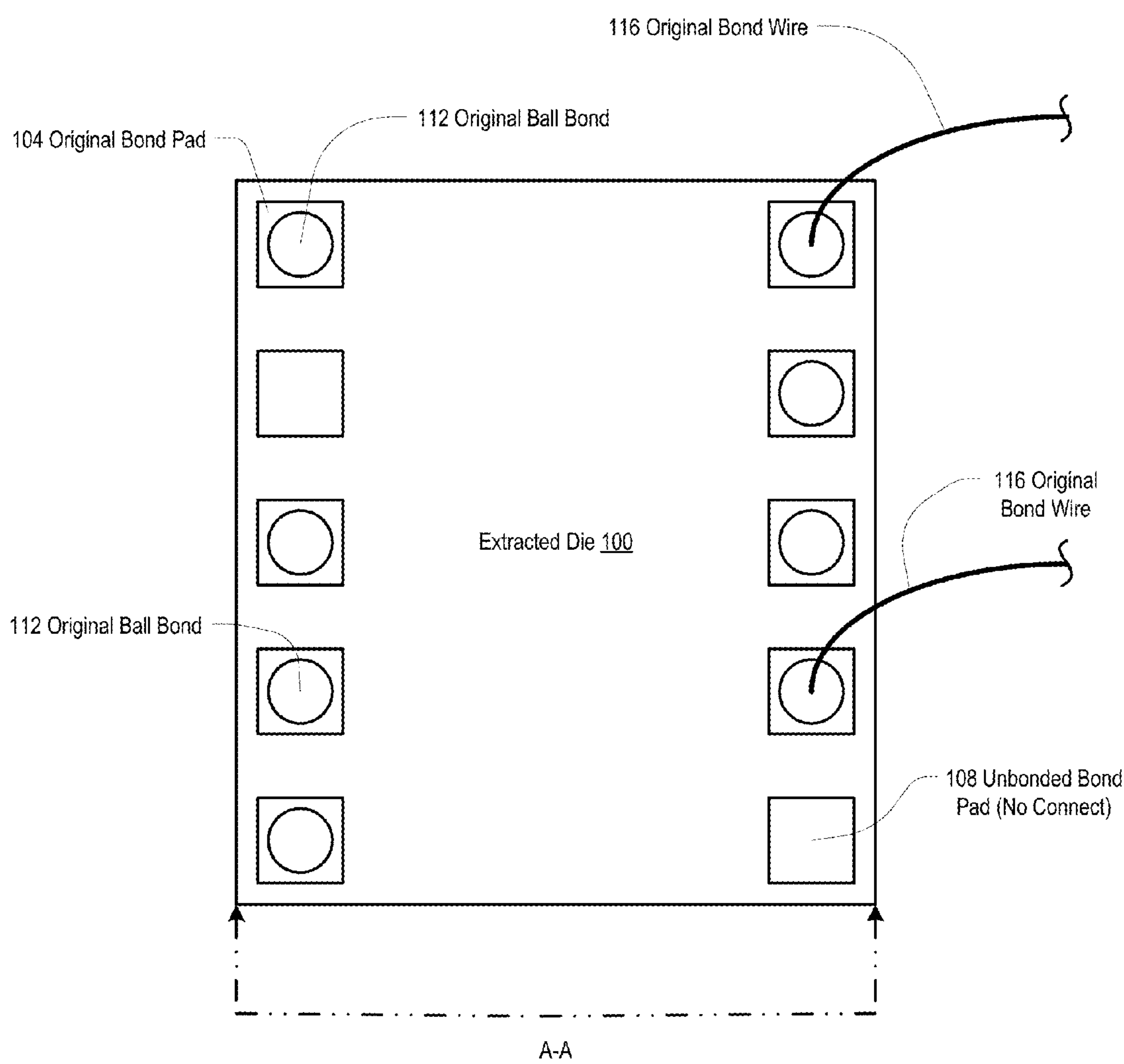


Fig. 2A Extracted Die Section A-A

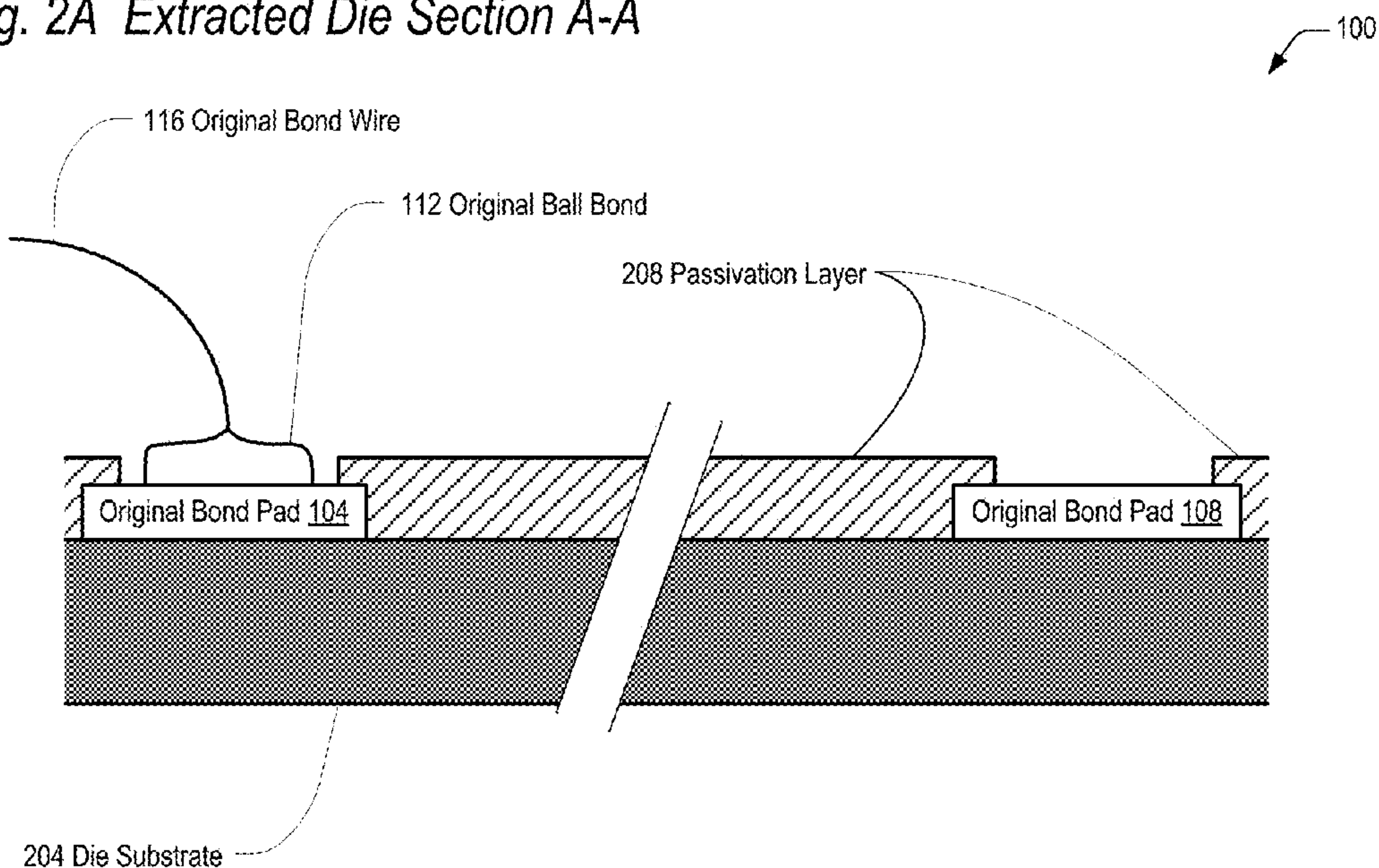


Fig. 2B Modified Extracted Die Section A-A After Original Ball Bond Removal

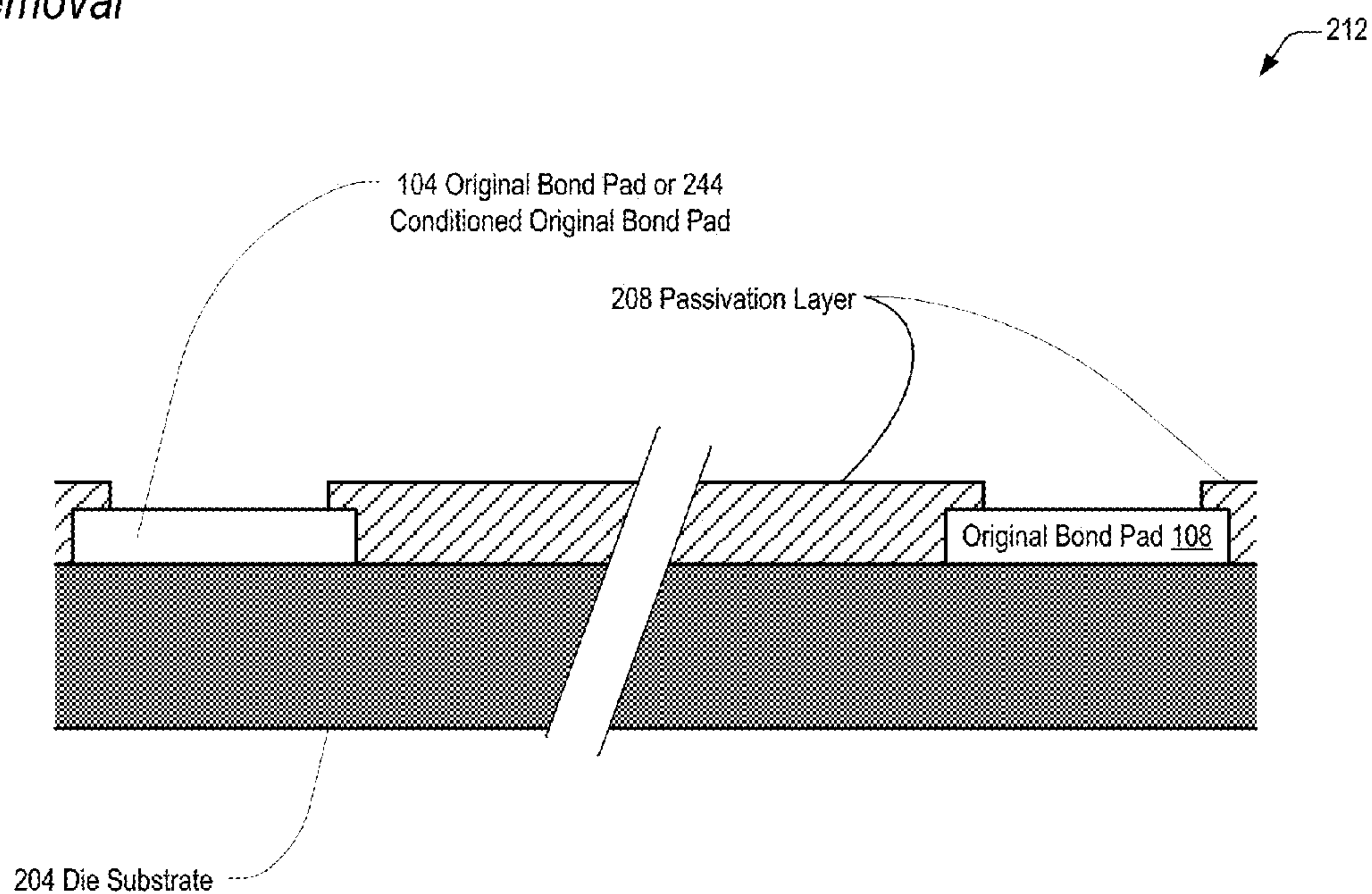


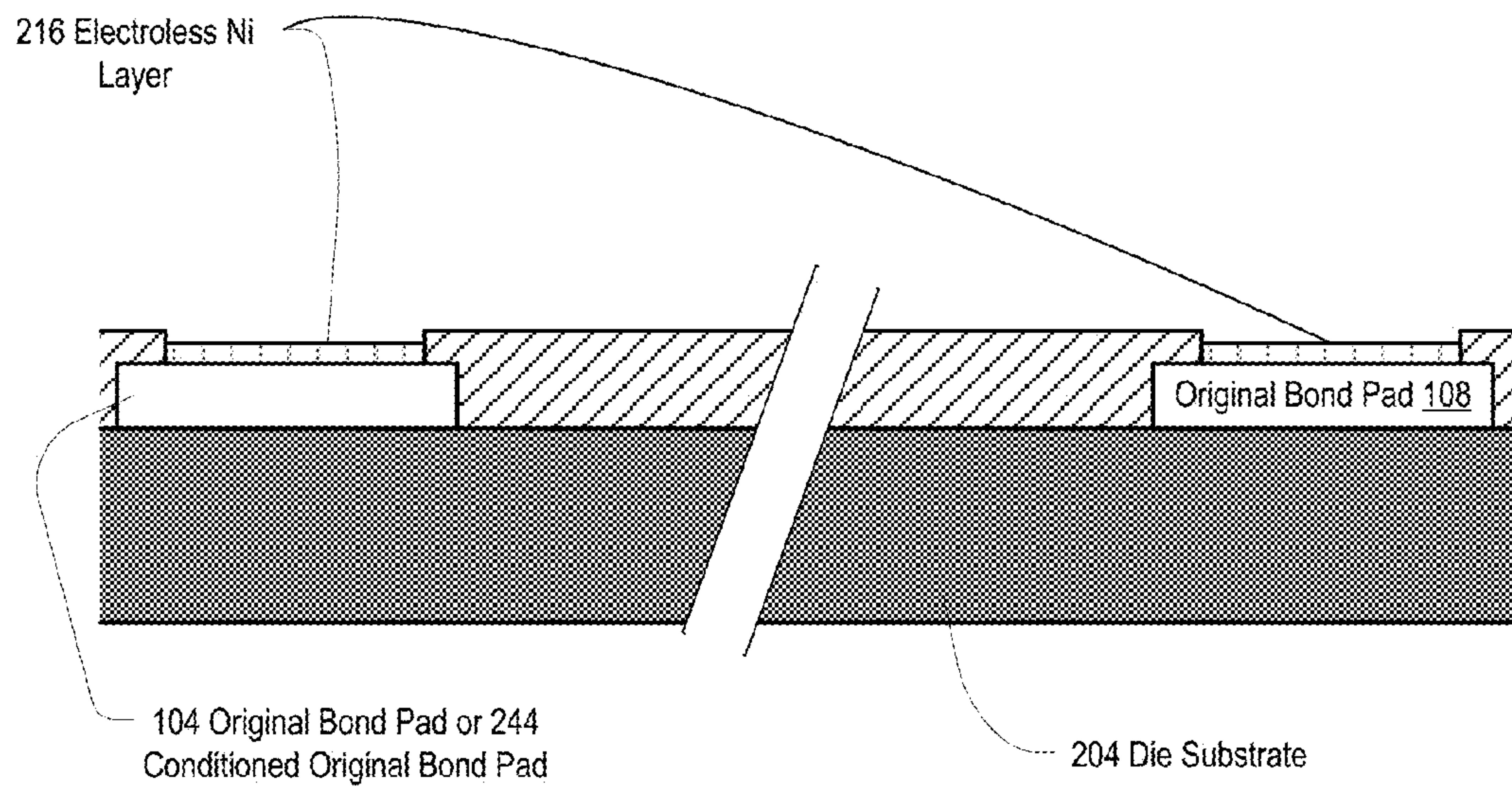
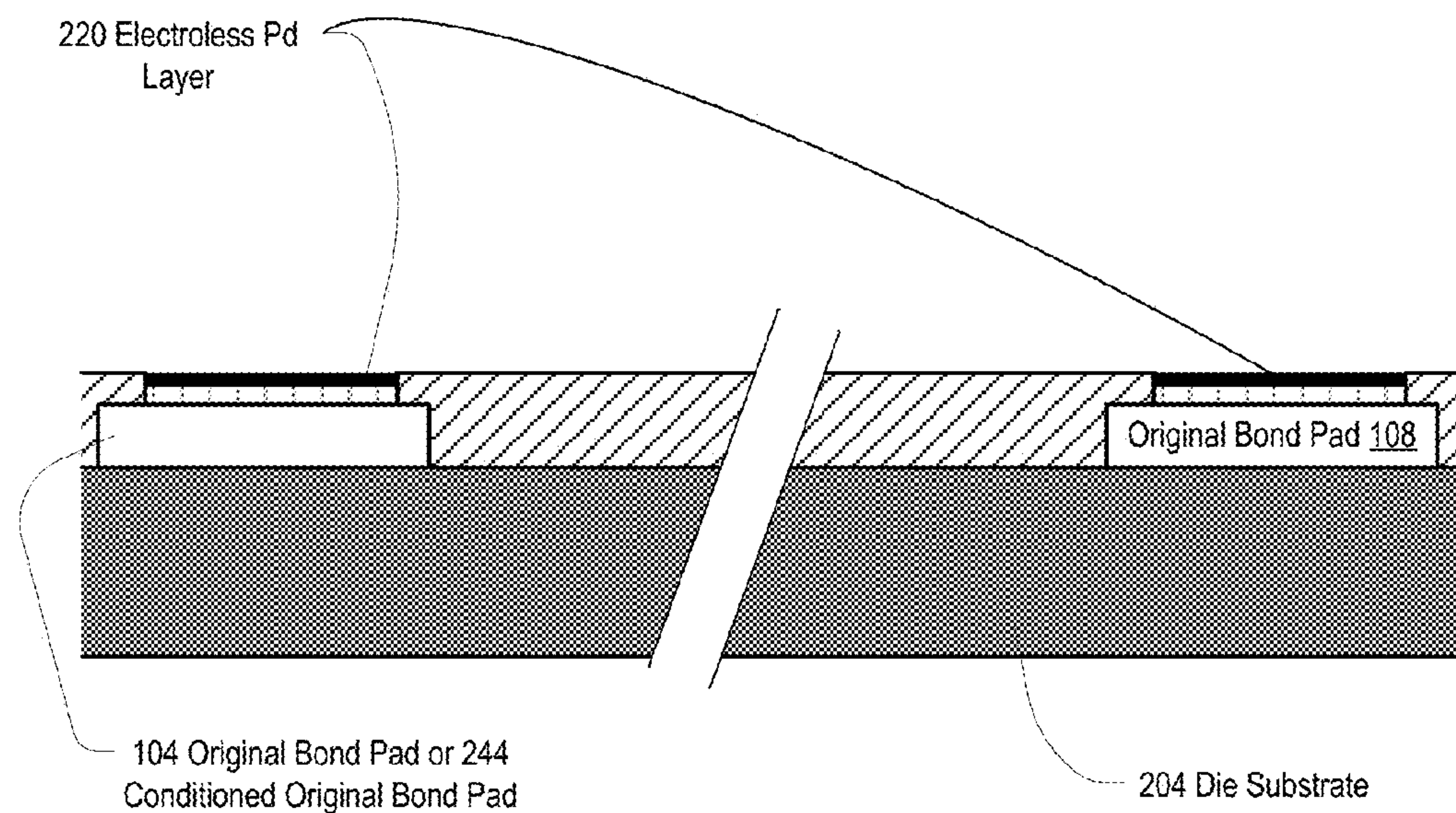
Fig. 2C Electroless Nickel Layer Application Section A-A*Fig. 2D Electroless Palladium Layer Section A-A*

Fig. 2E Immersion Gold Layer Application Section A-A

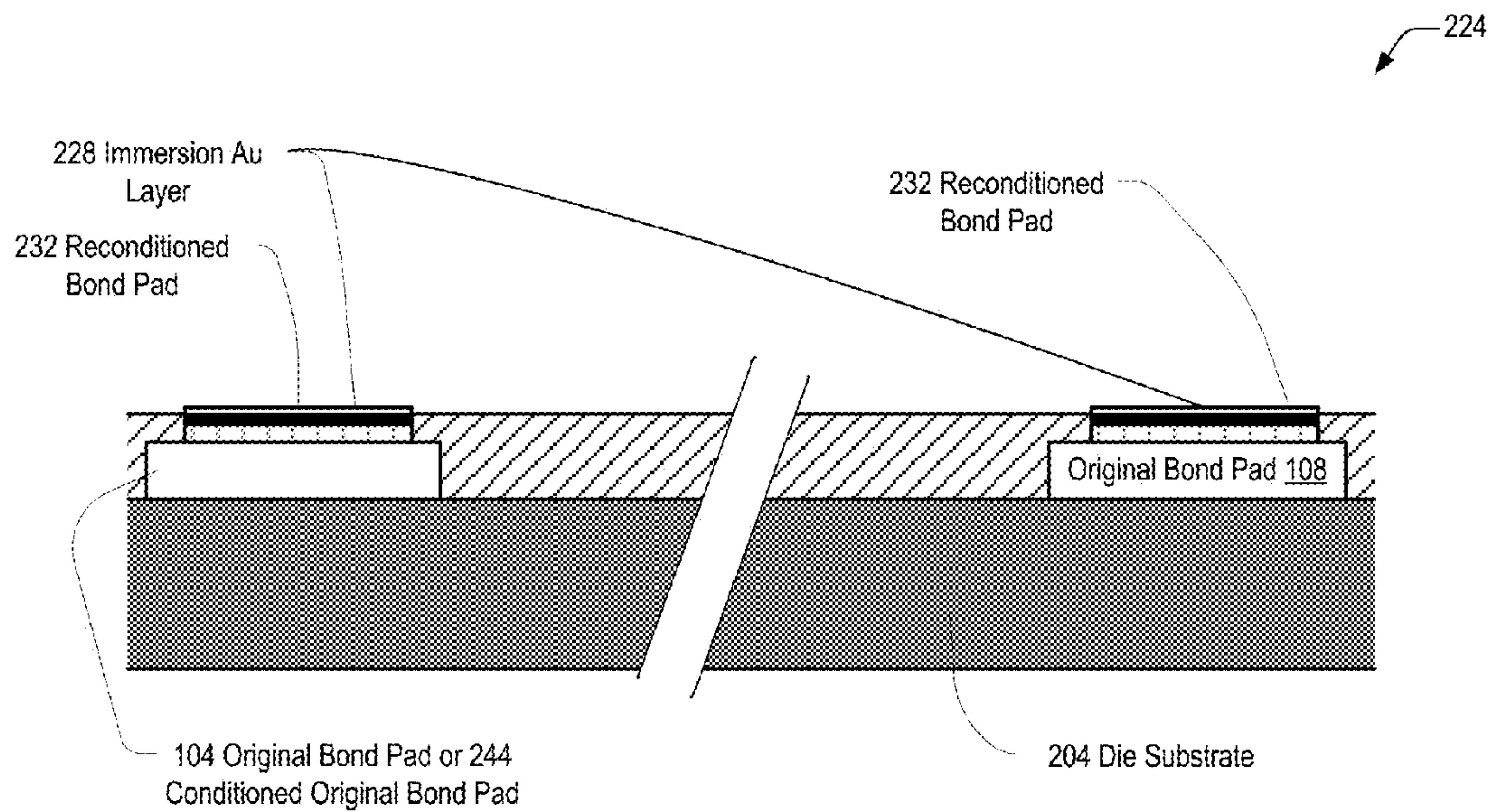


Fig. 2F New Bond Wires and Ball Bonds Section A-A

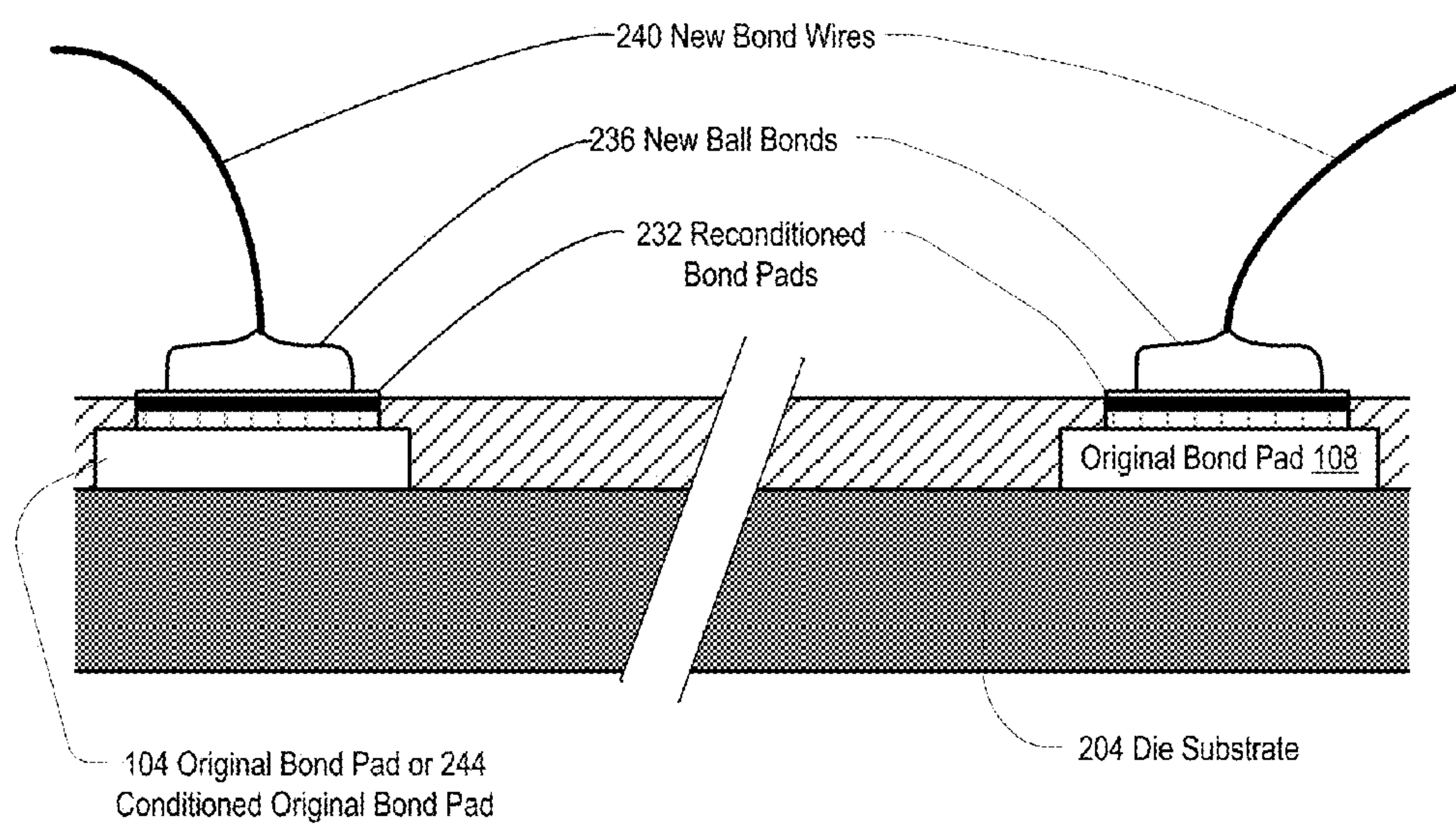
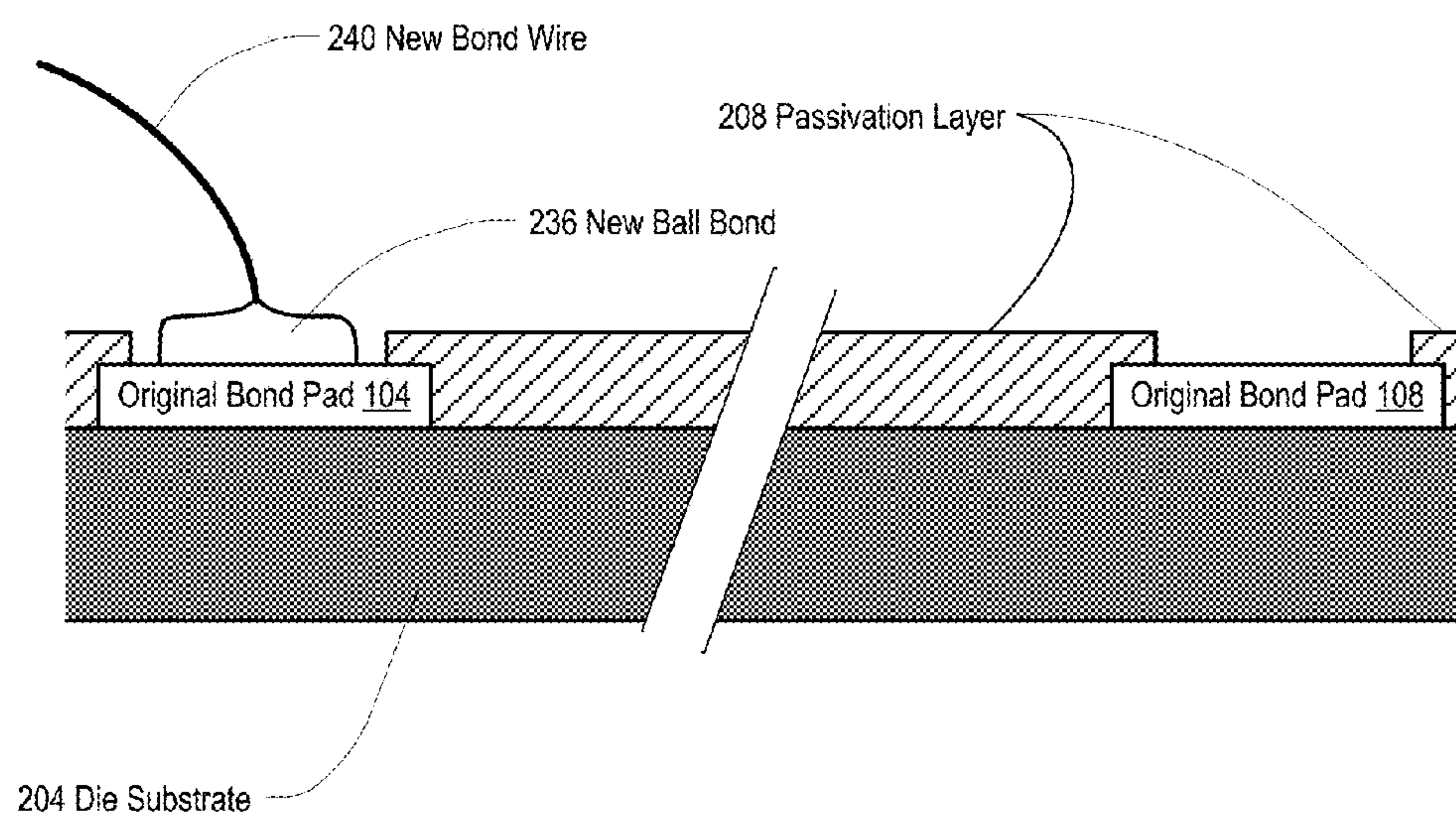


Fig. 3A Extracted Die Section A-A After Rebonding Process

300

*Fig. 3B Extracted Die Section A-A After Rebonding Process*

304

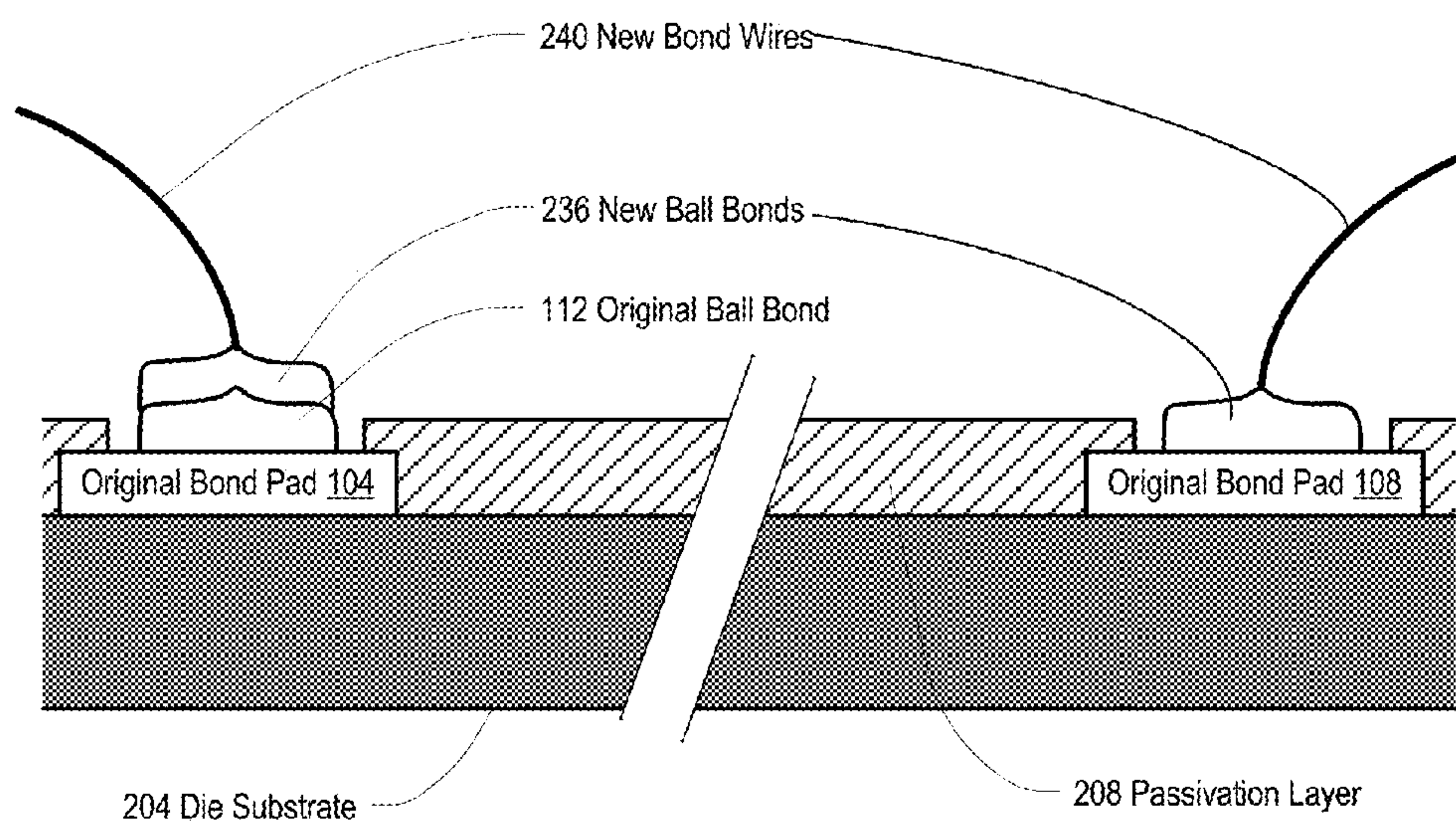


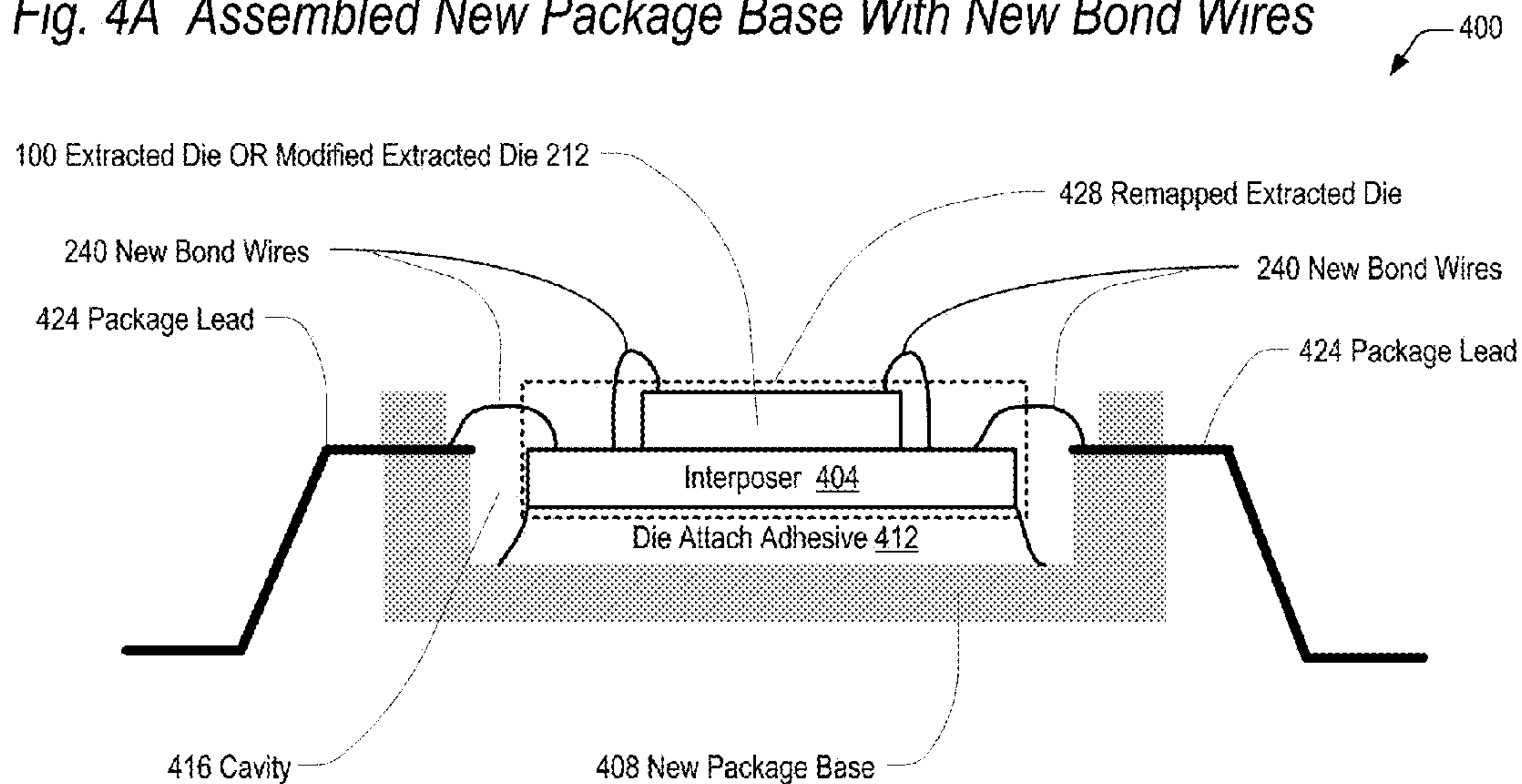
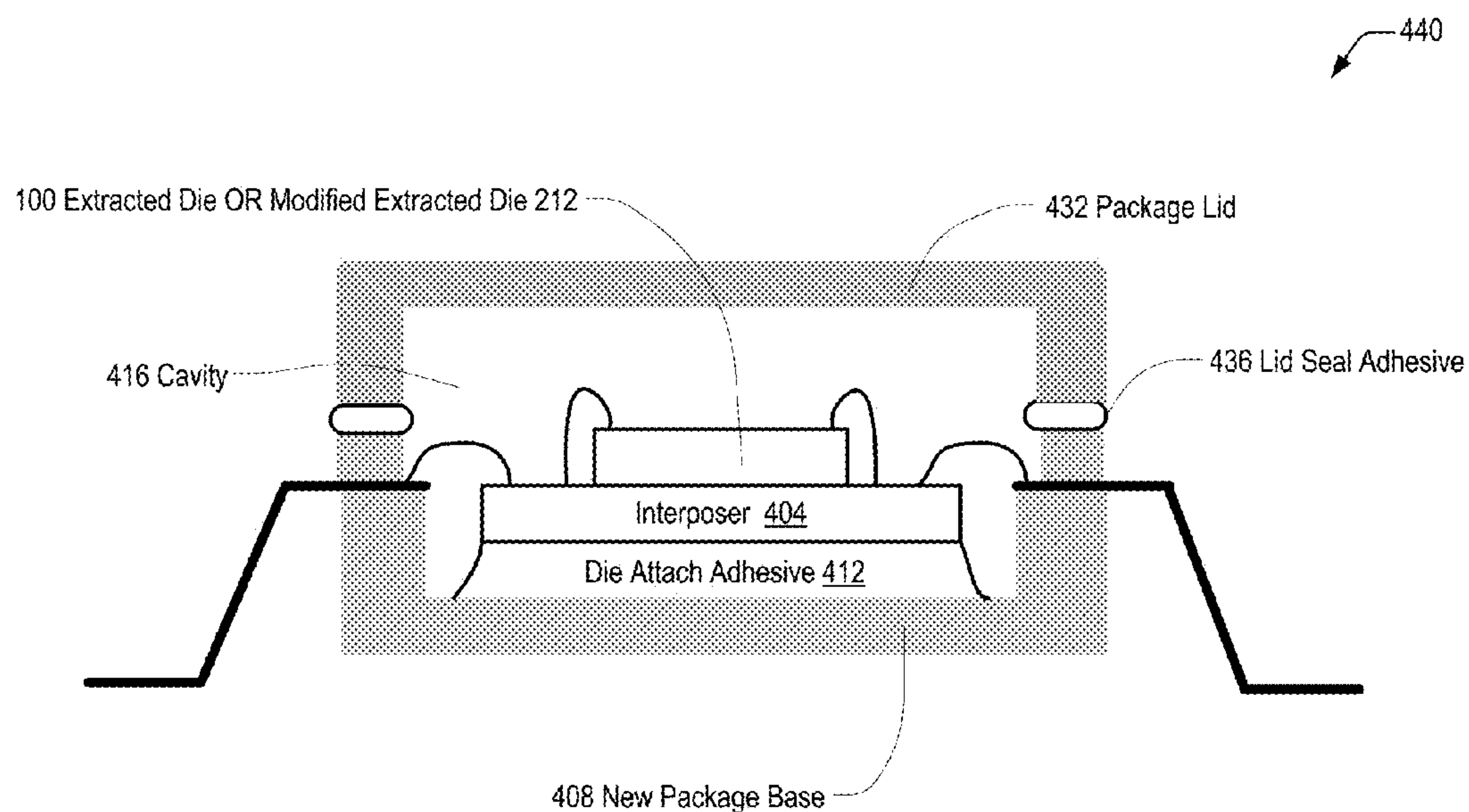
Fig. 4A Assembled New Package Base With New Bond Wires*Fig. 4B Assembled Non-Hermetic Package With Extracted Die*

Fig. 4C Assembled Hermetic Package With Extracted Die

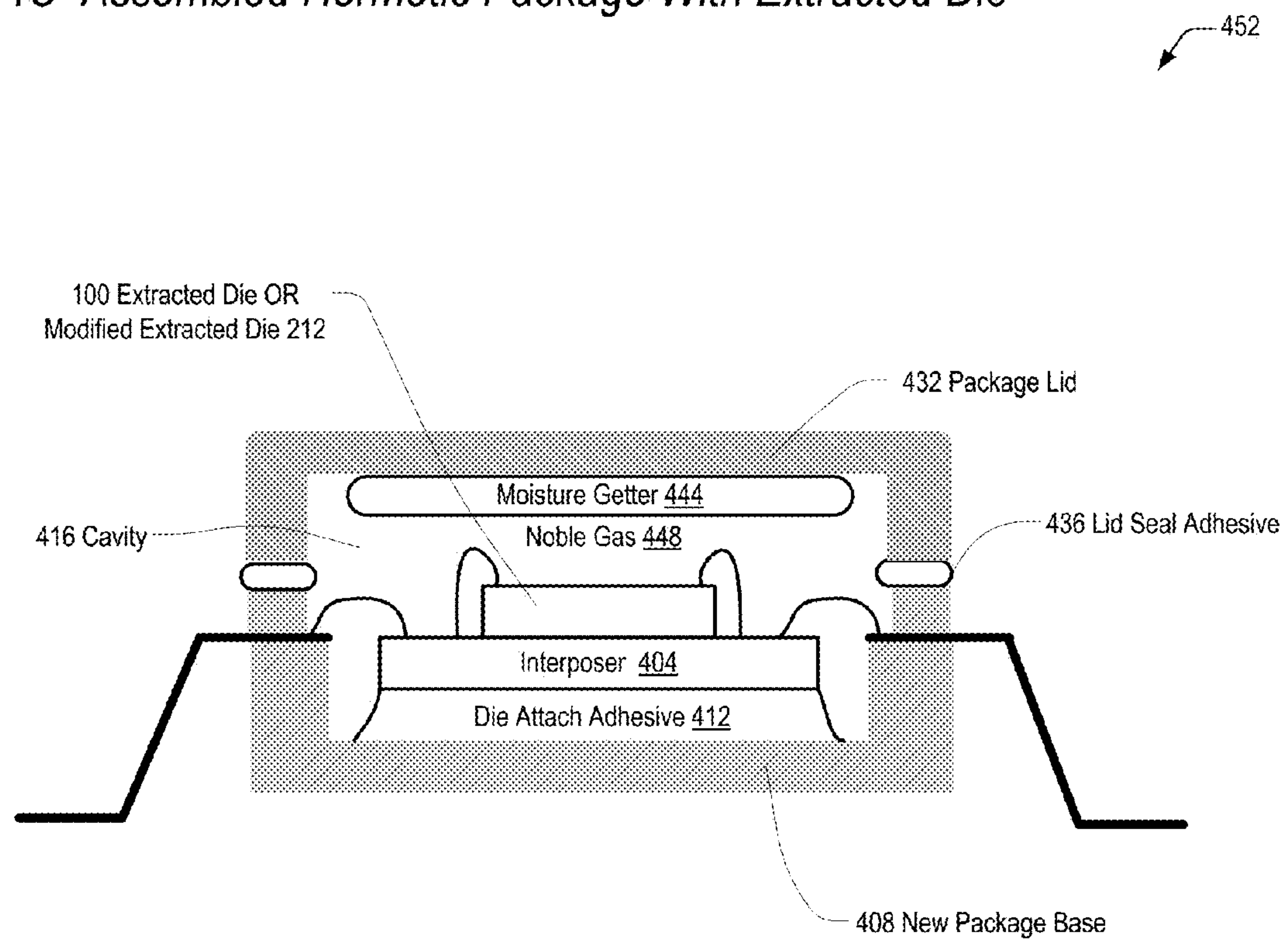


Fig. 5 Interposer for Extracted Die

404

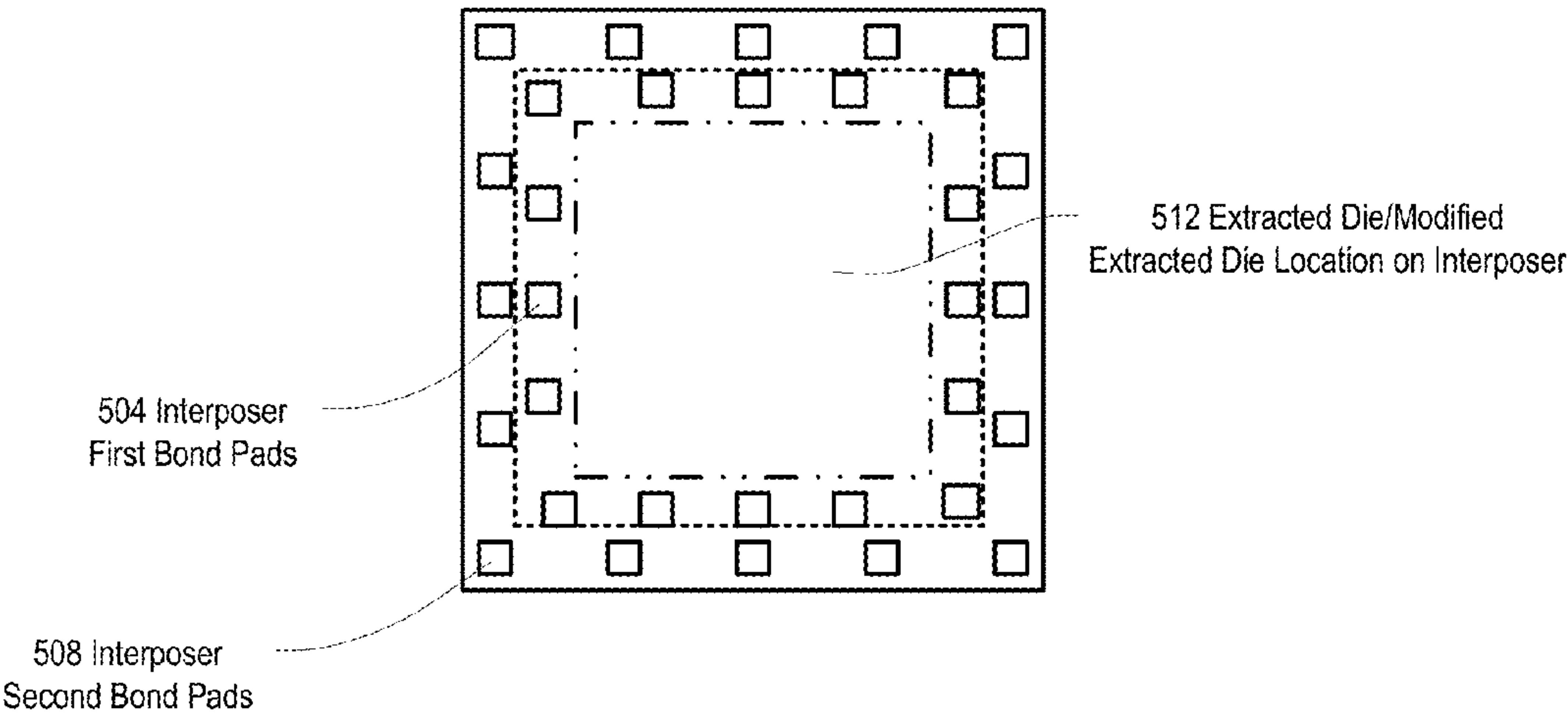


Fig. 6A Top View of New Package Base Before Wire Bonding

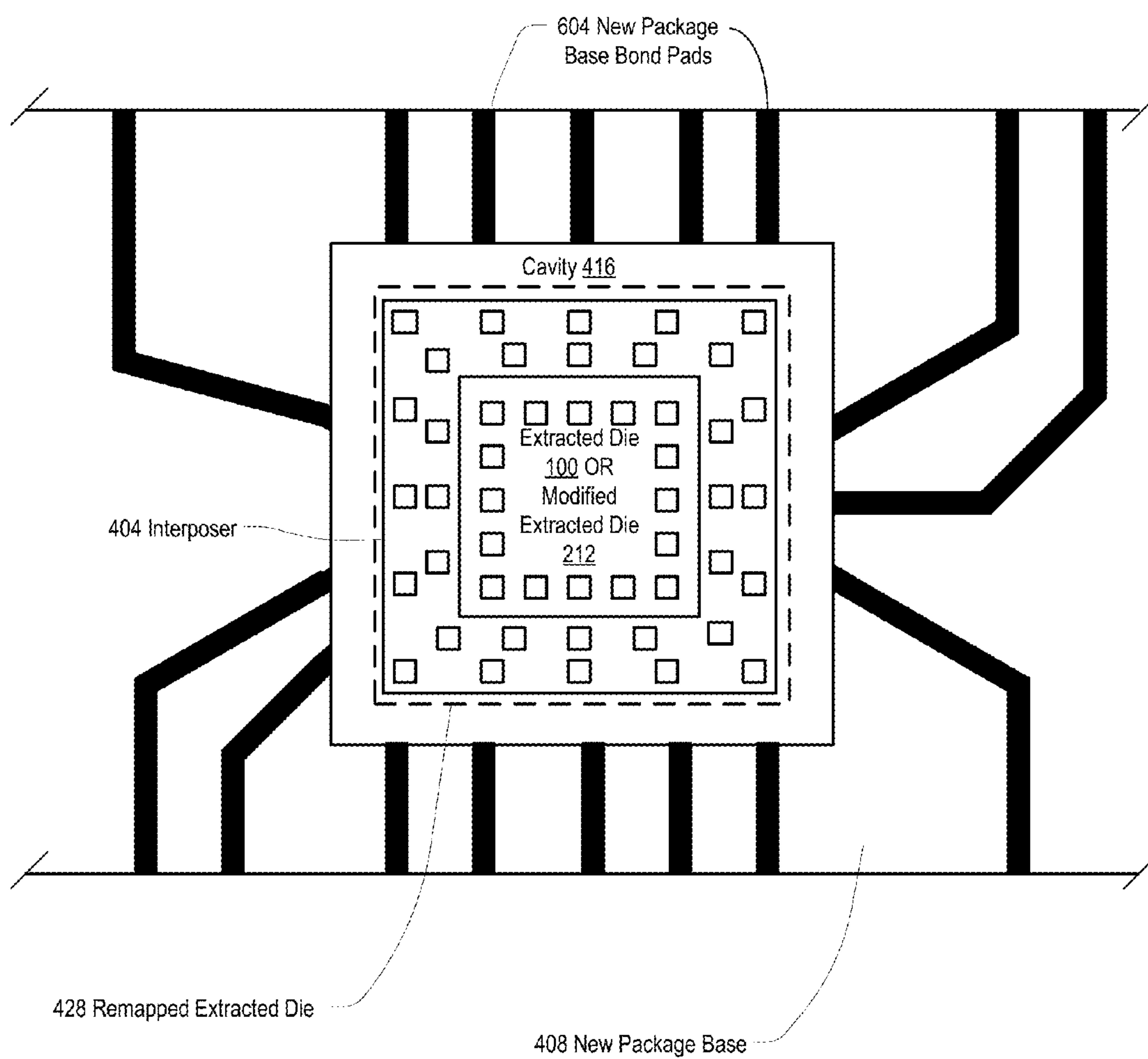


Fig. 6B Top View of New Package Base After Wire Bonding

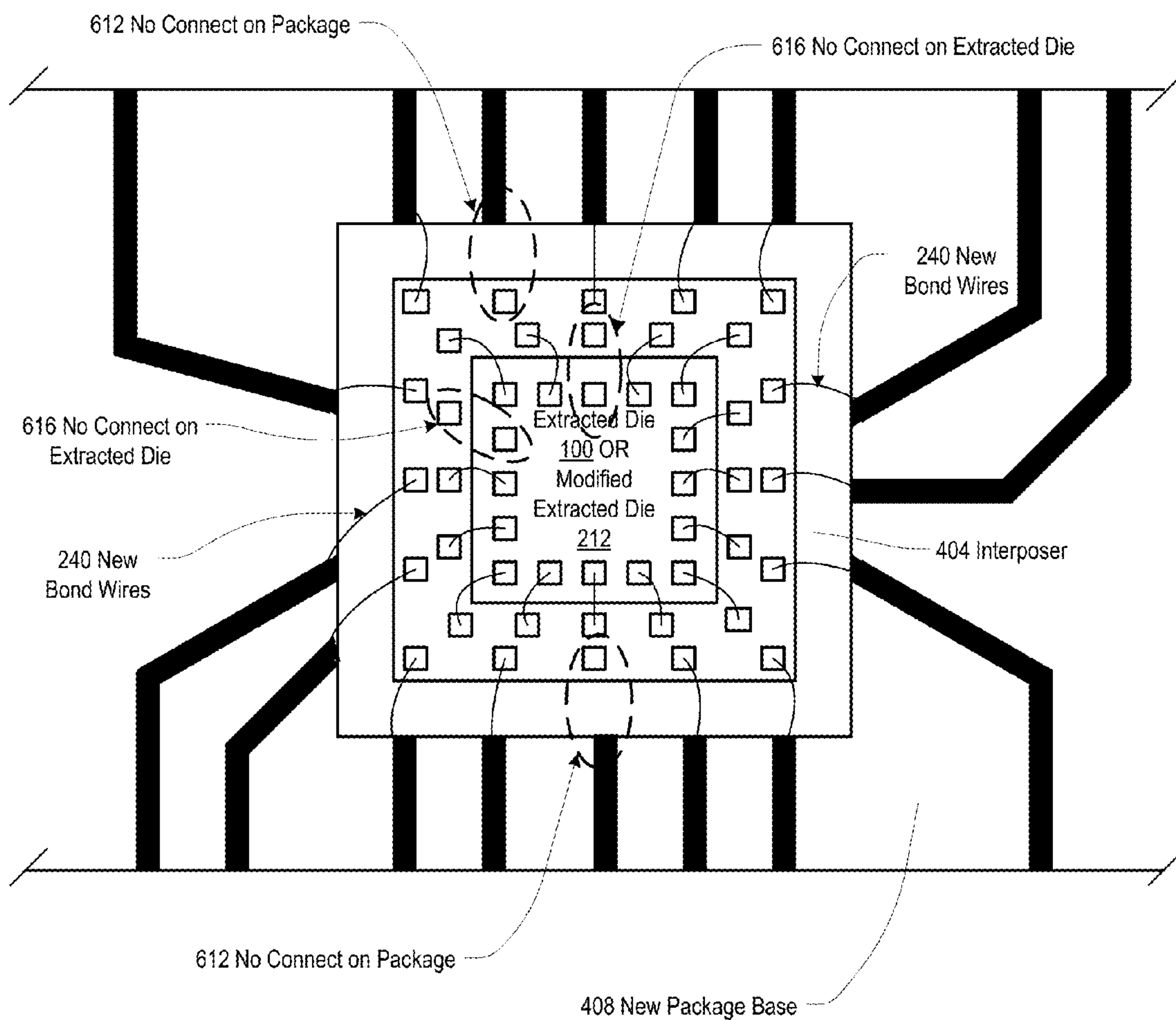


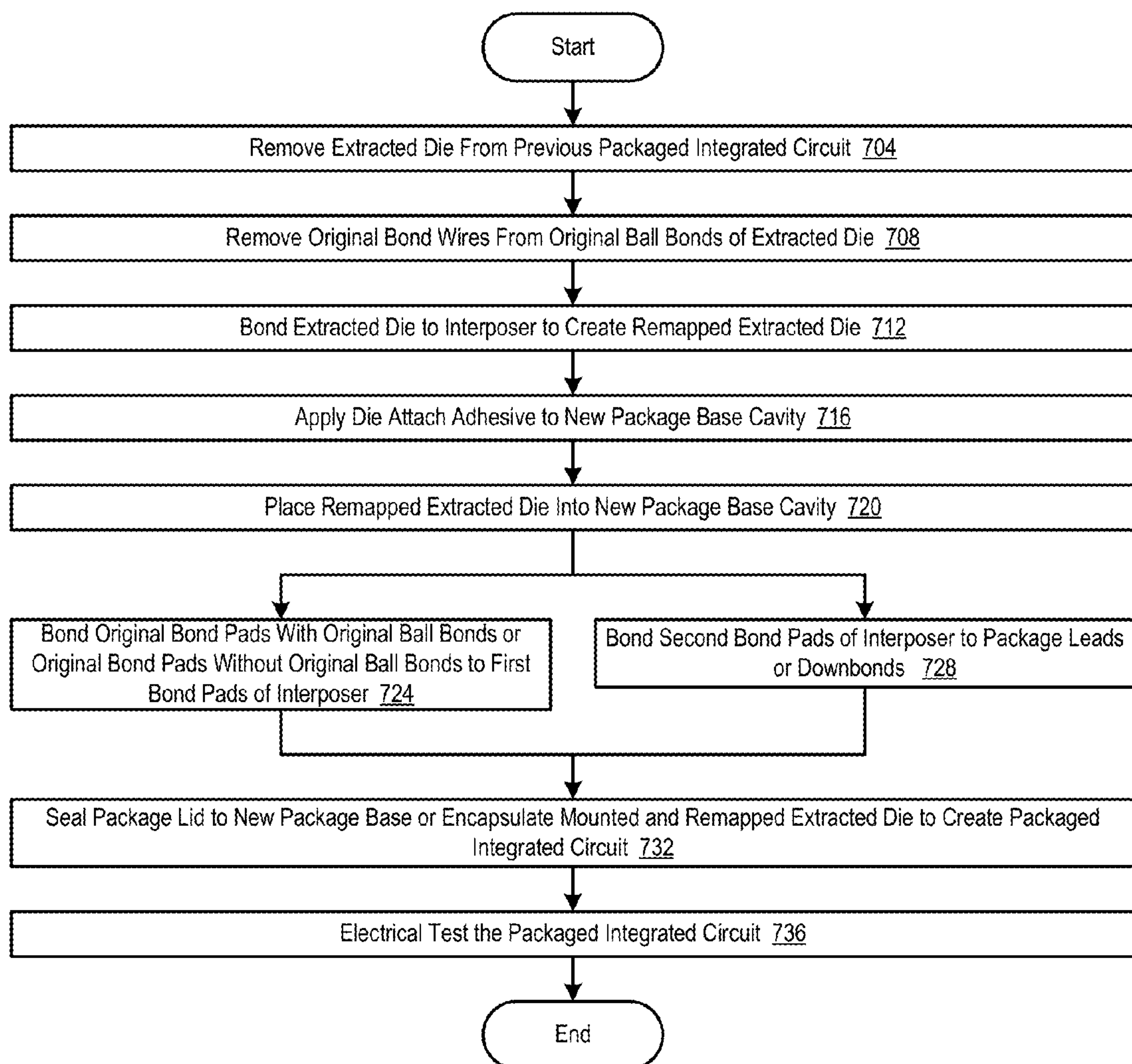
Fig. 7A Assembly Method for Packaged Integrated Circuit

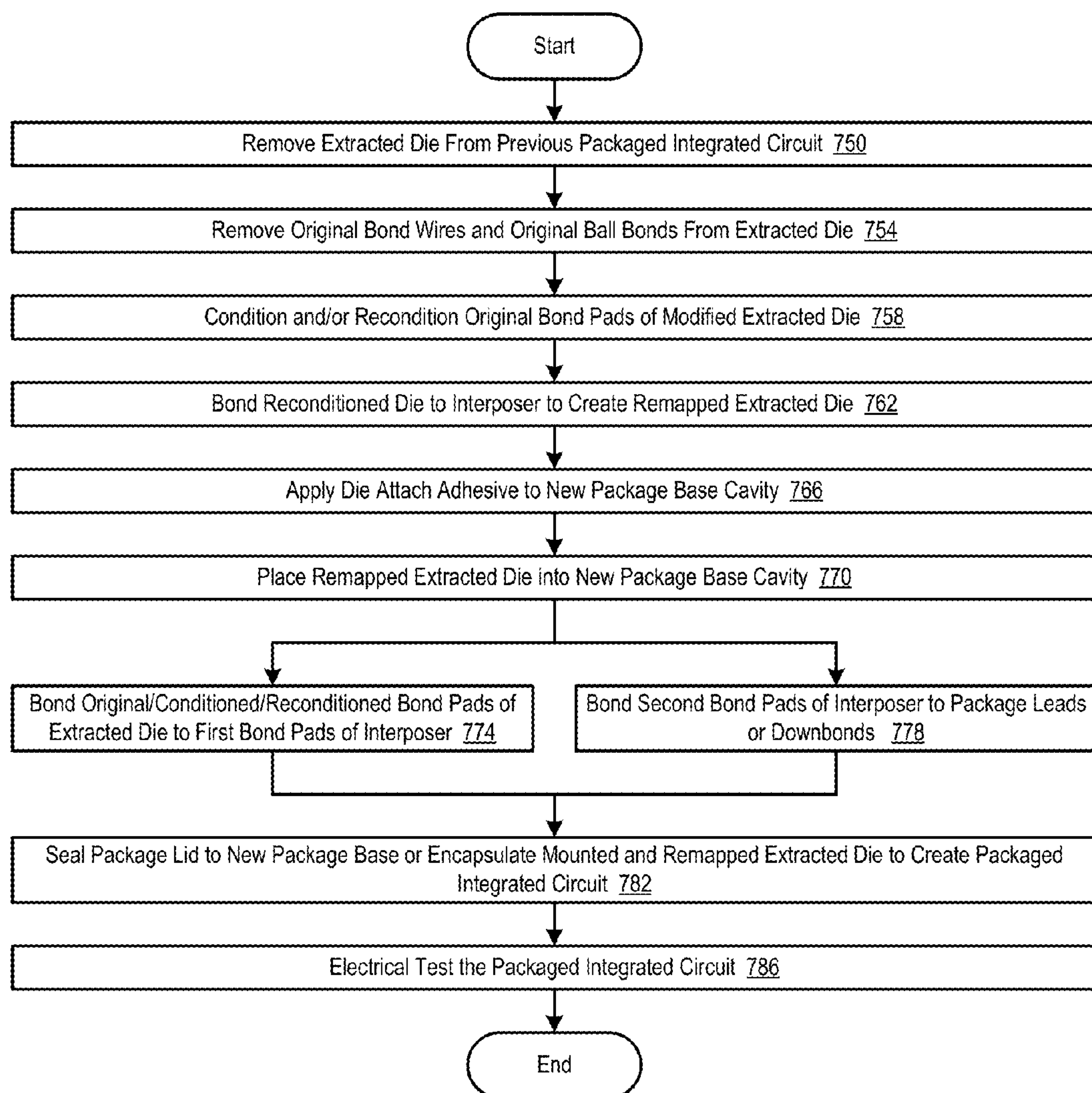
Fig. 7B Assembly Method for Packaged Integrated Circuit

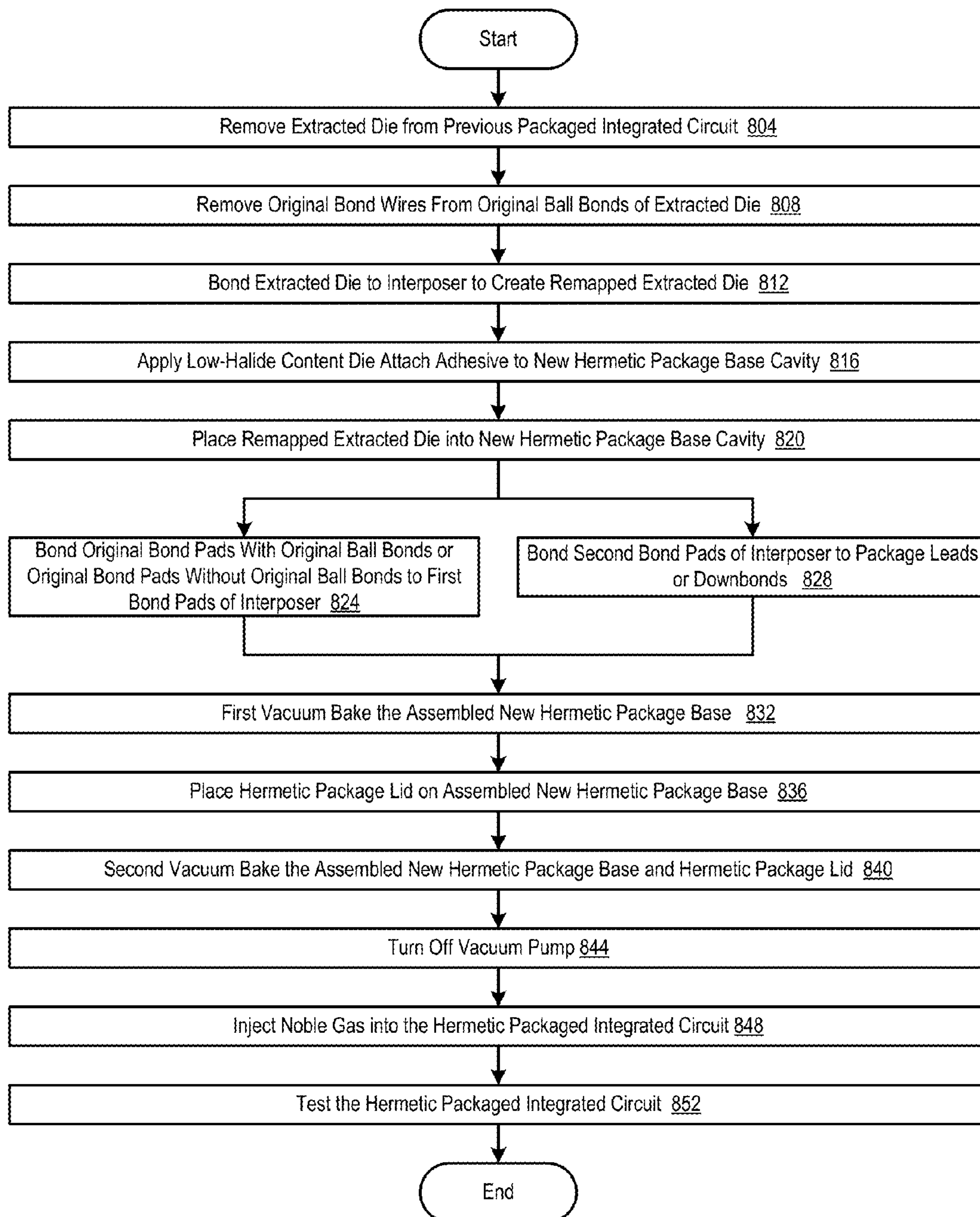
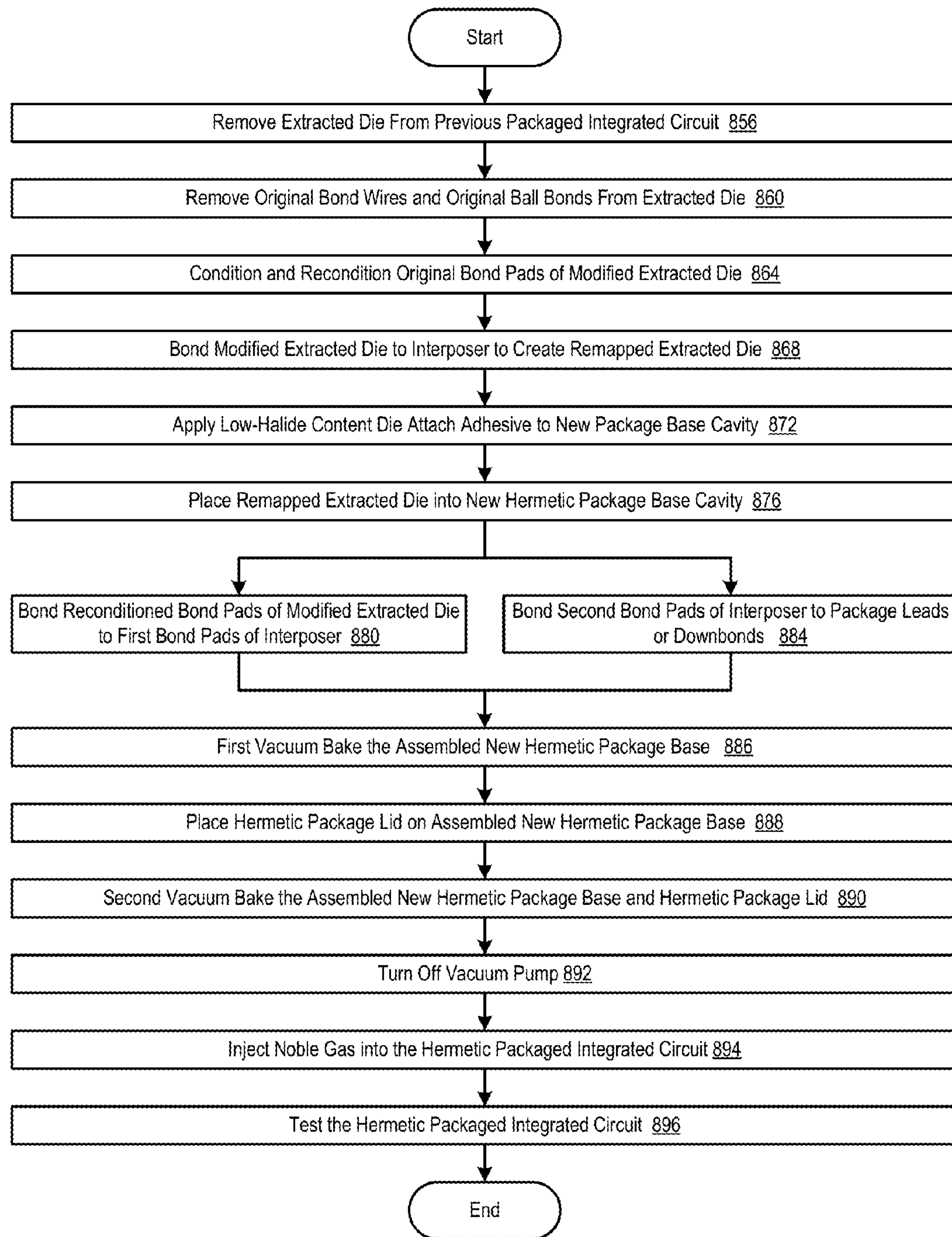
Fig. 8a Assembly Method for Hermetic Packaged Integrated Circuit

Fig. 8B Assembly Method for Hermetic Packaged Integrated Circuit

METHOD FOR REMAPPING A PACKAGED EXTRACTED DIE

CROSS REFERENCE TO RELATED APPLICATION(S)

This application is a Continuation-in-Part of U.S. application Ser. No. 13/623,603, filed Sep. 20, 2012, entitled ENVIRONMENTAL HARDENING TO EXTEND OPERATING LIFETIMES OF INTEGRATED CIRCUITS AT ELEVATED TEMPERATURES, which is hereby incorporated by reference for all purposes, which is a Continuation of U.S. application Ser. No. 13/283,293 filed Oct. 27, 2011, entitled ENVIRONMENTAL HARDENING TO EXTEND OPERATING LIFETIMES OF INTEGRATED CIRCUITS AT ELEVATED TEMPERATURES, now abandoned.

FIELD

The present invention is directed to integrated circuit packaging. In particular, the present invention is directed to methods for utilizing extracted dice in new packaged integrated circuits.

BACKGROUND

Integrated circuits are available in many different packages, technologies, and sizes. Most integrated circuits are available in plastic packages, which are generally intended for commercial operating environments at a low cost. Commercial operating environments have a specified operating range from 0° C. to 70° C. Integrated circuits for military applications have historically been packaged in either metal or ceramic hermetic packages, which are able to work reliably in more demanding environments than commercial integrated circuits. Military operating environments have a specified operating range from -55° C. to 125° C. In order to save costs, the military has purchased integrated circuits through COTS (Commercial Off-The-Shelf) programs. However, these components are generally commercial grade components in plastic packages, and not intended for demanding environments requiring the broader temperature range reliability and durability of ceramic and metal hermetically packaged integrated circuits.

Depending on size and complexity, integrated circuits are available in a wide range of packages. Although many older integrated circuits were packaged using through-hole technology packages, surface mount packages have dominated over the past several decades. Surface mount packages generally have circuit density, cost, and other advantages over through-hole integrated circuits. Examples of through-hole packages include DIP (dual-in-line plastic) and PGA (pin grid array). Examples of surface mount packages include SOIC (small-outline integrated circuit) and PLCC (plastic leaded chip carrier).

Integrated circuit packages generally consist of a semiconductor die placed within a package base and bonded to the base with a suitable die attach adhesive. In conventional technology, the die is electrically attached to a lead frame of the package base with discrete bond wires, which connect individual pads of the die with package leads. In most cases, the bond wires are gold, but in other environments can be copper or aluminum. Specialized equipment is required to attach the bond wires to the die pads the lead frame. Once all of the bond wires are attached, the package lid is bonded to the package base and the integrated circuit can be tested.

SUMMARY

The present invention is directed to solving disadvantages of the prior art. In accordance with embodiments of the present invention, a method for remapping an extracted die is provided. The method includes one or more of removing an extracted die from a previous integrated circuit package, the extracted die including a plurality of original bond pads having locations that do not correspond to desired pin assignments of a new package base and bonding an interposer to the extracted die. The interposer includes first bond pads configured to receive new bond wires from the plurality of original bond pads and second bond pads corresponding to desired pin assignments of the new package base, each individually electrically coupled to one of the first bond pads and configured to receive new bond wires from package leads or downbonds of the new package base.

In accordance with another embodiment of the present invention, a method for creating a packaged integrated circuit is provided. The method includes one or more of removing an extracted die including original bond pads from a previous packaged integrated circuit, removing one or more original bond wires from the extracted die, bonding the extracted die to an interposer including first bond pads electrically coupled to second bond pads, bonding the interposer to a new package base including package leads, providing new bond wires between original bond pads and first bond pads, providing new bond wires between second bond pads and package leads or downbonds, and sealing a package lid to the new package base.

In accordance with a further embodiment of the present invention, a method for assembling a new packaged integrated circuit is provided. The method includes one or more of removing an extracted die from a previous packaged integrated circuit, bonding an interposer including first bond pads electrically coupled to second bond pads to the extracted die, securing the extracted die bonded to the interposer within a cavity of a new package base, providing new bond wires between the extracted die and first bond pads and between second bond pads and package leads or downbonds of the new package base, and sealing a package lid to the new package base.

An advantage of the present invention is that it allows a packaged integrated circuit to be produced even if the die or wafers needed are out of production. Sometimes, the only way to obtain new packaged integrated circuits is to reuse extracted dice from previous packaged integrated circuits.

Another advantage of the present invention is it provides a way to repackage an extracted die for a different package and pinout than the extracted die was originally packaged for. There is no limit to the pinouts that may be thusly created, and by using different interposers, extracted dice may be utilized in many different packages and pinouts.

Additional features and advantages of embodiments of the present invention will become more readily apparent from the following description, particularly when taken together with the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a diagram illustrating an extracted die with original bond pads, original ball bonds, and original bond wires in accordance with embodiments of the present invention.

FIG. 2A is an illustration depicting a section A-A of an extracted die in accordance with embodiments of the present invention.

3

FIG. 2B is an illustration depicting a section A-A of a modified extracted die after original ball bond removal in accordance with embodiments of the present invention.

FIG. 2C is an illustration depicting a section A-A of an extracted die with electroless Nickel layer application in accordance with embodiments of the present invention.

FIG. 2D is an illustration depicting a section A-A of an extracted die with an electroless Palladium layer in accordance with embodiments of the present invention.

FIG. 2E is an illustration depicting a section A-A of an extracted die with an immersion Gold layer in accordance with embodiments of the present invention.

FIG. 2F is an illustration depicting a section A-A of an extracted die with new bond wires and new ball bonds in accordance with embodiments of the present invention.

FIG. 3A is an illustration depicting a section A-A of an extracted die after a first rebonding process in accordance with embodiments of the present invention.

FIG. 3B is an illustration depicting a section A-A of an extracted die after a second rebonding process in accordance with embodiments of the present invention.

FIG. 4A is an illustration depicting an assembled new package base with new bond wires in accordance with embodiments of the present invention.

FIG. 4B is an illustration depicting an assembled non-hermetic integrated circuit package with an extracted die in accordance with embodiments of the present invention.

FIG. 4C is an illustration depicting an assembled hermetic integrated circuit package with an extracted die in accordance with embodiments of the present invention.

FIG. 5 is an illustration depicting an interposer for an extracted die in accordance with embodiments of the present invention.

FIG. 6A is an illustration depicting a top view of a new package base before wire bonding in accordance with embodiments of the present invention.

FIG. 6B is an illustration depicting a top view of a new package base after wire bonding in accordance with embodiments of the present invention.

FIG. 7A is a flowchart illustrating an assembly method for a packaged integrated circuit in accordance with a first embodiment of the present invention.

FIG. 7B is a flowchart illustrating an assembly method for a packaged integrated circuit in accordance with a second embodiment of the present invention.

FIG. 8A is a flowchart illustrating an assembly method for a hermetic packaged integrated circuit in accordance with a third embodiment of the present invention.

FIG. 8B is a flowchart illustrating an assembly method for a hermetic packaged integrated circuit in accordance with a fourth embodiment of the present invention.

DETAILED DESCRIPTION

Integrated circuits are most commonly packaged in plastic packages using dice with Aluminum (Al) bond pads and Gold (Au) bond wires from the bond pads to the package leads and package cavity. Bond wires are attached to bond pads and package leads using thermosonic bonding, wedge bonding, or other processes well understood in the art.

In some cases, bare dice and wafers are generally not available. It is therefore highly desirable to obtain dice from previously packaged integrated circuits. Integrated circuit dice are then extracted from an existing package—usually plastic—and repackaged into a suitable package according to the component needs of the market. These extracted dice retain the original Au ball bonds on the Al die pads. In some

4

cases, extracted dice are repackaged into commercial plastic packages. In other cases, often military or environmentally hardened applications, extracted dice are repackaged into hermetic ceramic or metal packages.

The present invention is directed to integrated circuits and methods for removing extracted dice from a previous package and repackaging into a different package, generally with a different pinout from the previous package.

Referring now to FIG. 1, an extracted die 100 with original bond pads 104, 108, original ball bonds 112, and original bond wires 116 in accordance with embodiments of the present invention is shown. Extracted die 100 is an individual semiconductor die or substrate, and is usually fabricated in suitable technologies including Silicon (Si) and Gallium Arsenide (GaAs). Extracted die 100 may have a single die or multiple interconnected dice. Regardless whether extracted die 100 includes a single die or multiple interconnected dice, die circuitry is connected to original bond pads 104, 108 of the extracted die 100. Original bond pads 104, 108 are most commonly aluminum (Al) or copper (Cu) alloy pads, although the present invention is not limited to any particular bond pad 104, 108, 504, 508 or bond wire 116, 240 metallurgy.

Each previously used original bond pad 104 of the extracted die 100 may have an original ball bond 112 present, although one or more unbonded bond pads 108 may not have an original ball bond 112 present. In some cases, this is due to a no-connect in the previous integrated circuit package. When the extracted die 100 was present in whatever previous integrated circuit package was used for the extracted die 100, original bond wires 116 connected each of the original ball bonds 112 to a lead or a downbond of the previous integrated circuit package. FIG. 1 illustrates an exemplary extracted die 100 after it has been removed from the previous integrated circuit package. Therefore, some original bond wires 116 have been removed and some original bond wires 116 remain. In current technology packaged integrated circuits, the vast majority of bond wire interconnections are made with Gold (Au) thermosonic ball bonding. Extracted dice 100 are in the state shown in FIG. 1 at the beginning of the process of the present invention. Section A-A is used in FIGS. 2A-2F and 3A, 3B to illustrate a side view of extracted die 100.

Referring now to FIG. 2A, a diagram illustrating a section A-A of an extracted die 100 in accordance with embodiments of the present invention is shown. In order to show the assembly of the preferred embodiment of the present invention, a side view of the extracted die 100 is provided.

Extracted die 100 includes a die substrate 204 including various metallization layers known in the art. On the surface of the die substrate 204 are one or more original bond pads 104, 108. A passivation layer 208 is applied over the die substrate 204 in order to protect the circuits of the die substrate 204, and the passivation layer 208 is relieved at each of the original bond pads 104, 108 in order to provide bonding access.

Where original ball bonds 112 and original bond wires 116 are applied to original bond pads 104, 108, the original bond pads are original bond pads 104. Where no original ball bonds 112 and original bond wires 116 are applied to original bond pads 104, 108, the original bond pads are original bond pads 108. FIG. 2A illustrates the point at which the extracted die 100 has been removed from its' original package and one or more original ball bonds 112 and original bond wires 116 are present.

Referring now to FIG. 2B, a diagram illustrating a section A-A of a modified extracted die 212 after original ball bond

112 and original bond wire 116 removal in accordance with embodiments of the present invention is shown. A modified extracted die is an extracted die 100 with the original ball bonds 108 and original bond wires 116 removed. Although in some embodiments original gold ball bonds 112 may be removed by mechanical means, in most cases it is preferable to use chemical removal means by known processes. FIG. 2B illustrates the original ball bond 112 and original bond wire 116 removed from the original bond pad 104. Not shown in FIG. 2B is that after removing the original ball bond 112 and original bond wire 116, some amount of intermetallic residue and/or oxides will be present on the original bond pads 104. This generally requires removal to make sure there are no impurities, residues, or oxides on the original bond pads 104, 108. Removal is preferably performed using a mild acid wash. The acid wash is followed by an acid rinse that removes surface oxides present on the original bond pads 104, 108. For plating on an Aluminum surface, a zincate process is used to etch away a very fine layer of Aluminum from the original bond pads 104, 108 and redeposit a layer of Zinc (Zn) on the original bond pads 104, 108. The fine layer of Zinc will then act as a catalyst for the Nickel plating to follow. Once residues and oxides have been removed from the original bond pads 104, 108, in some embodiments the surface of the original bond pads 104, 108 is rendered to an increased degree of flatness by applying a lapping process. This has the added benefit of providing a uniformly smooth and consistent bond pad 104, 108 surface in preparation for following reconditioning/metallization (ENEPIG—electroless Nickel, electroless Palladium, immersion Gold, for example) or ball bonding operations. The various such processing steps described above, including removing original ball bonds and bond wires, impurities, residues, and oxides, various acid washes and rinses, and possibly lapping the surface, result in conditioned original bond pads 244.

Once in a clean and flat state, the conditioned original bond pads 244 or original bond pads 108 are ready to be reconditioned. Reconditioning of the present invention is a process whereby the original bond pads 108 or conditioned original bond pads 244 are built up by successive and ordered application of specific metallic layers prior to new wire bonding processes.

In one embodiment, after an extracted die 100 is removed from a packaged integrated circuit, only original bond wires 116 are removed—thus leaving original ball bonds 112 on less than all original bond pads 104 of the extracted die 100. Original ball bonds 112 must be removed prior to conditioning or reconditioning bond pads. Therefore, in some embodiments the metallic layers of the present invention are provided not to bare original bond pads 108, but rather original bond pads 104 following original ball bond 112 removal, or to any original bond pad 104, 108 intended to receive a new ball bond 236 and new bond wire 240. Conditioned original bond pads are original bond pads with original bond wires 116, original ball bonds 112, and residue/oxides removed. Reconditioned bond pads are conditioned original bond pads following application of the metallic layer structure shown and described with respect to FIGS. 2C-2E herein.

Referring now to FIG. 2C, a diagram illustrating a section A-A of electroless Nickel layer 216 application in accordance with embodiments of the present invention is shown. Electroless plating is more cost effective than electroplating since it does not require expensive photolithography and etch processes. However, electroless processes generally require thicker metal layers for good bondability.

A Nickel (Ni) layer 216 applied over conditioned original bond pads has been found to protect pad surfaces. Nickel possesses a much higher elastic modulus than either Copper (Cu) or Aluminum (Al), which leads Nickel to have high stiffness and fracture toughness and resist deflection and absorb energy during ball bonding processes. Thus, Nickel is a preferred metallic layer 216 for the initial layer application following original bond pad 104, 108 conditioning processes.

An electroless Nickel plating bath is very complex and contains more chemicals (i.e. reducing agents, complexant or chelating agents, stabilizers, etc) than the Nickel source alone. These bath components are known in the art and perform specific functions during the chemical reaction. They are important in order to obtain a good quality Nickel deposit and must be monitored carefully during processing.

The plating rate of Nickel is a controllable parameter during the plating process, which in turn affects the final surface roughness. A fast plating rate will obviously increase the process throughput, but fast plating rates can also result in a rougher Nickel finish. Therefore, a careful balance must be maintained between processing speed and surface quality. If the Nickel surface is too rough, the next successive metal layers to be plated over the Nickel will follow the contours and also result in a rougher surface. Both surface hardness and roughness have a strong effect on wire bondability and bond strength. Harder and rougher surfaces are typically less bondable. For wire bonding applications, the electroless Nickel layer 216 is generally 120-240 microinches thick.

Referring now to FIG. 2D, a diagram illustrating a section A-A of Electroless Palladium layer 220 application in accordance with embodiments of the present invention is shown. Electroless Palladium (Pd) 220 is applied over the Electroless Nickel (Ni) 216 layer of FIG. 2C in order to inhibit Nickel diffusion into the Immersion gold layer 224 applied afterward.

Palladium plating was first investigated as a replacement for purely gold plating in order to alleviate the high cost of gold plating. Palladium and Palladium-Nickel alloys were initially developed for contact wear resistance in connector applications, but other technical advantages were identified as usage grew. Not only is a pure Palladium layer very hard, but it is also very dense which assists as a diffusion barrier. As with the Electroless Nickel layer 216, the Electroless Palladium layer 220 requires a catalyst pretreatment to prepare the surface for deposition. The metal source is typically a Palladium-Ammonia compound with a hydrazine reducing agent for metal deposition. For wire bonding applications, the Electroless Palladium layer 220 is generally 2-4 microinches thick, approximately 2 orders of magnitude thinner than the Electroless Nickel layer 216.

Referring now to FIG. 2E, a diagram illustrating a section A-A of immersion Gold layer 228 application in accordance with embodiments of the present invention is shown. The immersion Gold layer 228 is applied over the electroless Palladium layer 220, and provides the top layer of the reconditioned bond pads 232. Gold has long been a mature plating process for semiconductor applications. Two types of Gold plating processes through chemical reactions are used today: immersion and autocatalytic. Immersion Gold plating 228 is a self-limiting galvanic displacement process, where no reducing agent is required. For wire bonding applications, the immersion Gold layer 228 is generally at least 1-2 microinches thick, and preferably thicker. Following the process step of FIG. 2E, the die is a reconditioned die 224.

Because the ENEPIG plating process uses Gold as the wire bonding layer with Gold bond wire, there is no Al-

minum (Al)-Gold (Au) interface that can degrade and corrode. Thus, the ENEPIG plating process produces more reliable wire bonding interfaces and is preferred for high temperature applications over previous processes that maintained Al—Au interfaces and utilized moisture getter, noble gas insertion, and vacuum bakes to purge moisture from integrated circuit packages.

Referring now to FIG. 2F, a diagram illustrating a section A-A of new bond wires **240** and ball bonds **236** in accordance with embodiments the present invention is shown. The combination of the electroless Nickel layer **216**, electroless Palladium layer **220**, and the immersion Gold layer **228** produces a reconditioned bond pads **232**. New gold bond wires **240** may be thermosonically welded to reconditioned bond pads **232**, and will produce a new Gold ball bond **236** at each new bond wire **240** location.

In thermosonic welding, the interface temperature is typically between 125° C. and 220° C. For ball bonding, the new bond wire **240** is threaded through a capillary-shaped tool, and a spark melts the end of the wire forming a ball at the bottom of the tool. The bond (weld) is formed when the tool under load presses or deforms the ball against the heated bonding pad and ultrasonic energy is applied, completing the process.

Referring now to FIG. 3A, a diagram illustrating a section A-A of an extracted die **100** after a first rebonding process **300** in accordance with embodiments of the present invention is shown. The assembly step shown in FIG. 3A immediately follows the assembly step shown in FIG. 2B, where all original ball bonds **112** and original bond wires **116** have been removed from the extracted die **100**, but a bond pad reconditioning process such as an ENEPIG process as shown in FIGS. 2C-2F is not used.

Extracted die **100** includes a die substrate **204** including various metallization layers known in the art. On the surface of the die substrate **204** are one or more original bond pads **104**, **108** or conditioned original bond pads **244**. A passivation layer **208** is applied over the die substrate **204** in order to protect the circuits of the die substrate **204**, and the passivation layer **208** is relieved at each of the original bond pads **104**, **108** in order to provide bonding access.

Referring now to FIG. 3B, a diagram illustrating a section A-A of an extracted die **100** after a second rebonding process **304** in accordance with embodiments of the present invention is shown. The assembly step shown in FIG. 3B immediately follows the assembly step shown in FIG. 2A, where all original bond wires **116** have been removed from the extracted die **100**, but one or more original ball bonds **112** still remain and a bond pad reconditioning process such as an ENEPIG process as shown in FIGS. 2C-2F is not used. New ball bonds **236** and new bond wires **240** are provided either above original ball bonds **112** or original bond pads **108**.

Referring now to FIG. 4A, an illustration depicting an assembled package base **400** with new bond wires **240** in accordance with embodiments of the present invention is shown. The assembled package base **400** includes a new package base **408**. In one embodiment, the new package base **408** is a non-hermetic new package base **408**. In another embodiment, the new package base **408** is a hermetic new package base **408**. In non-hermetic applications, new package base **408** is generally plastic. If the new package base **408** is a hermetic package base **408**, it may be formed from ceramic, metal, or glass materials.

After conditioning and/or reconditioning any original bond pads **104**, **108** of the extracted die **100**, the extracted die **100** is bonded to an interposer **404** with a suitable die

attach adhesive **412**. The extracted die **100** bonded to the interposer **404** is referred to herein as a remapped extracted die **428**. This is described in more detail in FIG. 6A. In one embodiment, the original bond pads **104**, **108** are prepared by removing original bond wires **116**. In other embodiments, the original bond pads **104**, **108** are prepared by removing original ball bonds **112** and original bond wires **116**, and removing any traces of original ball bonds **112**, residues, oxides, and other deposits from the original bond pads **104** (i.e. conditioning processes as described herein). In some embodiments, the original bond pads **104**, **108** are buffed, polished, or lapped before adding any new ball bonds **236** and new bond wires **240**.

The new package base **408** includes a cavity **416** into which the remapped extracted die **428** is placed. Die attach adhesive **412** is applied to the new package base **408** such that when the extracted die **100** is inserted into the new package base cavity **416**, the die attach adhesive **412** makes simultaneous contact with both the new package base **408** and the extracted die **100**. Although not shown for clarity, a thin layer of die attach adhesive **412** would bond the extracted die **100** to the interposer **404**.

In embodiments where the new package base **408** is a component of a hermetic package **452**, die attach adhesive **412** is a low-halide compound adhesive, where a low halide compound has less than 10 parts per million (ppm) halide. Die attach adhesive **412** therefore bonds the extracted die **100** to the new package base **408**, and protects the integrity of the interior of the assembled package base **400**. It has been well established that halogens in an Au—Al bond interface degrade Au—Al bond strength since out-gassed products from adhesives containing halogens rapidly corrode Al metallization in integrated circuits at high temperatures, thus reducing product lifetime at high temperatures.

Associated with the new package base **408** are a series of package leads **424**, which provide interconnection between circuitry of the extracted die **100** and circuitry of a printed circuit board on which the packaged integrated circuit **440**, **452** is eventually mounted. For example, if an S0-24 ceramic package is used for the packaged integrated circuit, 24 package leads **424** would be present, configured as 12 package leads **424** on each of two opposite sides of the new package base **408**. If a PLCC-68 ceramic package is used for the integrated circuit, 68 package leads **424** would be present, configured as 17 package leads **424** on each of the four sides of the new package base **408**. The present invention may be used for any type of previous integrated circuit package or any type of new hermetic **452** or non-hermetic **440** integrated circuit package.

After mounting the remapped extracted die **428** into the new package base **408** using a die attach adhesive **412**, new bond wires **240** are then attached as described in more detail in FIG. 6B. New bond wires **240** are commonly 1-3 mils in diameter, but may be any usable diameter. In one embodiment, a new ball bond **236** is formed on top of an original ball bond **112**. In other embodiments, a new ball bond **236** is formed on top of original bond pads **108**. In a preferred embodiment, new bond wires **240** are Gold (Au) bond wires. In other embodiments, new bond wires **240** are Aluminum (Al) or Copper (Cu) bond wires.

Referring now to FIG. 4B, an illustration depicting an assembled non-hermetic integrated circuit package **440** with an extracted die **100** in accordance with embodiments of the present invention is shown. Packaged integrated circuit **440** is Assembled package base **400** with a package lid **432** attached. Where the new package base **408** and package lid **432** are non-plastic materials, lid seal adhesive **436** is

generally required. In non-hermetic applications, package lid **432** is generally plastic and is molded to a plastic new package base **408** with an encapsulation process. In such cases, a lid seal adhesive **436** may not be required.

Referring now to FIG. 4C, an illustration depicting an assembled hermetic integrated circuit package **452** with an extracted die **100** in accordance with embodiments of the present invention is shown. Packaged hermetic integrated circuit **452** includes the assembled hermetic package base **400** of FIG. 4A and additional components described below.

For a hermetic integrated circuit package **452** including a hermetic new package base **408**, once all new bond wires **240** are bonded between package leads **424** and downbonds and the remapped extracted die **428**, the assembled package base **400** including remapped extracted die **428**, die attach adhesive **412**, new package base **408**, package leads **424**, and new bond wires **240**, may be first and second vacuum baked according to the processes of parent application Ser. No. 13/623,603.

The assembled hermetic integrated circuit package **452** including low halide die attach adhesive **412**, noble inert gas **448**, and moisture getter **444** is used for a high-temperature application exposure (greater than 150 degrees Celsius) with original bond pads **104** where the original ball bonds **112** were not removed and/or the original bond pads **104**, **108** were not reconditioned **232**.

Referring now to FIG. 5, an illustration depicting an interposer **404** for an extracted die **100** in accordance with embodiments of the present invention is shown. Interposer **404** is a substrate that the extracted die **100** is mounted on one side of, and translates original bond pad **104**, **108**, conditioned original bond pad, or reconditioned bond pad **232** locations into bond pad locations that match a desired pinout of packaged integrated circuits **440**, **452**. Interposer **404** is a substrate or other material such as FR-4, Kapton, Teflon, or Polyamide suitable for mounting within a new package base **408** and carrying electrical signals to and from the extracted die **100** and package leads **424** or downbonds.

Interposer **404** includes a location **512** for mounting the extracted die **100** or modified die **212** on a specified side of interposer **404**. Extracted die **100** may be secured to interposer **404** with die attach adhesive **412**, an epoxy, or other chemical and/or mechanical means known in the art. In most embodiments, extracted die **100** is mounted centrally on the interposer **404** in order to facilitate wire bonding. However, in some embodiments the extracted die **100** may not be centrally mounted on interposer **404** for various reasons.

Interposer **404** includes a first set of bond pads **504** generally oriented around the periphery of the extracted die/modified die Location **512**. The first set of bond pads **504** provide attachment points for new bond wires **240** between the extracted die **100** and the interposer **404**.

In general, each of the first set of bond pads **504** is electrically connected to each of a second set of bond pads **508** via rerouting circuitry within the interposer **404**. However, it is not a requirement that every such pad **504**, **508** be thusly connected. The second set of bond pads **508** is generally oriented around the periphery of the interposer **404**. The second set of bond pads **508** provide attachment points for new bond wires **240** between the interposer **404** and package leads **424** and downbonds of the new integrated circuit package base **408**.

In most applications, the interposer **404** is designed so that the second bond pads **508** are as close as possible to the package base bond pad **604** or package lead **424** that each second bond pad **508** gets bonded to. This may require routing connections between some first bond pads **504** and

second bond pads **508** across most of the interposer **404**. To some extent the routing length of such connection may be mitigated by orienting the extracted die/modified die location **512** clockwise or counterclockwise on the interposer **404**, and this must be independently evaluated for each extracted die **100**/modified die **212** and interposer **404** combination.

Referring now to FIG. 6A, an illustration depicting a top view of a new package base **408** before wire bonding in accordance with embodiments of the present invention is shown. The remapped extracted die **608** is securely mounted in the cavity **416** of the new package base **408** with die attach adhesive **412**. The new package base **408** has a plurality of package base bond pads **604**, which provide a conduction path to the package leads **424** on the exterior of the new package base **408**. One package lead **424** is provided on the exterior of the new package base **408** for every package base bond pad **604**. The new package base **408** has different pin assignments than the previous package base the extracted die **100** was removed from.

Referring now to FIG. 6B, an illustration depicting a top view of a new package base **408** after wire bonding in accordance with embodiments of the present invention is shown. FIG. 6B illustrates the same point in the assembly process as shown in FIG. 4A. The new package base **408** is fully assembled, and is ready for a package lid **432** to be added or else encapsulation as a molded packaged integrated circuit **440**.

As shown in FIG. 6B, the new package base **408** has new bond wires **240** added. New bond wires **240** connect original bond pads **104**, **108** of the extracted die **100** or modified die **212** to the first bond pads **504** (usually but not necessarily, closest to the extracted die **100** or modified die **212**) of the interposer **404**. Other new bond wires **240** connect the second bond pads **508** (usually but not necessarily, closest to the edge of the interposer **404**) of the interposer **404** to package base bond pads **604**.

It is possible that some original bond pads **104**, **108** of the extracted die **100**/modified die **212** and Package base bond pads **604** will be no connects. No connects will not have a new bond wire **240** or new ball bond **236** attached. In FIG. 6B, there are two no connects **616** on the original bond pads **104**, **108** of the extracted die **100**, and two no connects **612** on the package base bond pads **604**. However, there may practically be any number of no connects, including zero.

Referring now to FIG. 7A, a flowchart illustrating an assembly method for a packaged integrated circuit **440** in accordance with a first embodiment of the present invention is shown. Flow begins at block **704**.

At block **704**, an extracted die **100** is removed from from previous packaged integrated circuit. The extracted die **100** will have at least one original ball bond **112** and one original bond wire **116**. It is possible that some or all existing original bond wires **116** will be removed during the die extraction process. Flow proceeds to block **708**.

At block **708**, original bond wires **116** are removed from original ball bonds **112** of extracted die **100**, if any original bond wires **116** are still present. Flow proceeds to block **712**.

At block **712**, the extracted die **100** is bonded to the interposer **404** to create a remapped extracted die **608**. Flow proceeds to block **716**.

At block **716**, die attach adhesive **412** is applied to the package base cavity **416**. Flow proceeds to block **720**.

At block **720**, the remapped extracted die **608** is placed into the package base cavity **416** to secure the remapped extracted die **608** to the new package base **408**. As an alternative to blocks **712**-**720**, the interposer **404** may first be

11

bonded to the new package base **408**, then the extracted die **100** may be bonded to the interposer **404**. Flow proceeds to blocks **724** and **728**.

At block **724**, new bond wires **240** are provided between the extracted die **100** and the first set of bond pads **504** of the interposer **404**. If there is an original ball bond **112** on an original bond pad **104** of the extracted die **100**, a new ball bond **236** is bonded to the original ball bond **112** as shown in FIG. 3B. Flow proceeds to block **732**.

At block **728**, new bond wires **240** are provided between the second bond pads **508** of the interposer **404** and package leads **424** or downbonds, as required. It should be noted that steps **724** and **728** may be completed in any order, depending on what new bond wire **240** installation produces the most efficient and reliable process. Flow proceeds to block **732**.

At block **732**, the package lid **432** is sealed to the assembled package base **400**, or alternatively, the non-hermetic packaged integrated circuit **440** is encapsulated. Flow proceeds to block **736**.

At block **736**, the packaged integrated circuit **440** is electrically tested. Electrical testing includes continuity tests or functional tests, or both. If the packaged integrated circuit **440** has passed the electrical tests, and the package leads **424** are properly trimmed, the packaged integrated circuit **440** is marked and is a complete new packaged integrated circuit **440** ready for use. Flow ends at block **736**.

Referring now to FIG. 7B, a flowchart illustrating an assembly method for a packaged integrated circuit **440** in accordance with a second embodiment of the present invention is shown. Flow begins at block **750**.

At block **750**, an extracted die **100** is removed from from previous packaged integrated circuit. The extracted die **100** will have at least one original ball bond **112** and one original bond wire **116**. It is possible that some or all existing original bond wires **116** will be removed during the die extraction process. Flow proceeds to block **754**.

At block **754**, original bond wires **116** and original ball bonds **112** are removed from extracted die **100**. Flow proceeds to block **758**.

At block **758**, the original bond pads **104**, **108** are conditioned and/or reconditioned. Conditioning includes removing any impurities from original bond pads **104**, **108** and reconditioning applies an ENEPIG surface treatment in order to prepare the original bond pads **104**, **108** to accept new ball bonds **236** and new bond wires **240**. Instead of reconditioning, the original bond pads **104**, **108** may be cleaned and/or lapped with all metallic and chemical residues removed. Flow proceeds to block **762**.

At block **762**, the extracted die **100** is bonded to the interposer **404** to create a remapped extracted die **608**. Flow proceeds to block **766**.

At block **766**, die attach adhesive **412** is applied to the package base cavity **416**. Flow proceeds to block **770**.

At block **770**, the remapped extracted die **608** is placed into the package base cavity **416** to secure the remapped extracted die **608** to the new package base **408**. As an alternative to blocks **762-770**, the interposer **404** may first be bonded to the new package base **408**, then the extracted die **100** may be bonded to the interposer **404**. Flow proceeds to blocks **774** and **778**.

At block **774**, new bond wires **240** are provided between original bond pads **104**, **108**, conditioned original bond pads, or reconditioned bond pads **232** of the extracted die **100** and the first set of bond pads **504** of the interposer **404**. Flow proceeds to block **782**.

At block **778**, new bond wires **240** are provided between the second bond pads **508** of the interposer **404** and package

12

leads **424** or downbonds, as required. It should be noted that steps **774** and **778** may be completed in any order, depending on what new bond wire **240** installation produces the most efficient and reliable process. Flow proceeds to block **782**.

At block **782**, the package lid **432** is sealed to the assembled package base **400**, or alternatively, the non-hermetic packaged integrated circuit **440** is encapsulated. Flow proceeds to block **786**.

At block **786**, the packaged integrated circuit **440** is electrically tested. Electrical testing includes continuity tests or functional tests, or both. If the packaged integrated circuit **440** has passed the electrical tests, and the package leads **424** are properly trimmed, the packaged integrated circuit **440** is marked and is a complete new packaged integrated circuit **440** ready for use. Flow ends at block **786**.

Referring now to FIG. 8A, a flowchart illustrating an assembly method for a hermetic packaged integrated circuit **452** in accordance with a third embodiment of the present invention is shown. Flow begins at block **804**.

At block **804**, an extracted die **100** is removed from from previous packaged integrated circuit. The extracted die **100** will have at least one original ball bond **112** and one original bond wire **116**. It is possible that some or all existing original bond wires **116** will be removed during the die extraction process. Flow proceeds to block **808**.

At block **808**, original bond wires **116** are removed from original ball bonds **112** of extracted die **100**, if any original bond wires **116** are still present. Flow proceeds to block **812**.

At block **812**, the extracted die **100** is bonded to the interposer **404** to create a remapped extracted die **608**. Flow proceeds to block **816**.

At block **816**, a low halide content die attach adhesive **412** is applied to the package base cavity **416**. Flow proceeds to block **820**.

At block **820**, the remapped extracted die **608** is placed into the package base cavity **416** to secure the remapped extracted die **608** to the new package base **408**. As an alternative to blocks **812-820**, the interposer **404** may first be bonded to the new package base **408**, then the extracted die **100** may be bonded to the interposer **404**. Flow proceeds to blocks **824** and **828**.

At block **824**, new bond wires **240** are provided between the extracted die **100** and the first set of bond pads **504** of the interposer **404**. If there is an original ball bond **112** on an original bond pad **104** of the extracted die **100**, a new ball bond **236** is bonded to the original ball bond **112** as shown in FIG. 3B. Flow proceeds to block **832**.

At block **828**, new bond wires **240** are provided between the second bond pads **508** of the interposer **404** and package leads **424** or downbonds, as required. It should be noted that steps **724** and **728** may be completed in any order, depending on what new bond wire **240** installation produces the most efficient and reliable process. Flow proceeds to block **832**.

At block **832**, the assembled hermetic package base **400** is first vacuum baked. The assembled hermetic package base **400** includes the hermetic new package base **408**, package leads **424**, remapped extracted die **608**, the die attach adhesive **412**, and new bond wires **240**. The process of first vacuum baking is illustrated in FIG. 11 of application Ser. No. 13/623,603. Flow proceeds to block **836**.

At block **836**, the assembled hermetic package base **400** is removed from the vacuum baking apparatus and the hermetic package lid **432** is placed on the assembled hermetic package base **400**. The hermetic package lid **432** is placed in proper orientation such that the combination of the hermetic package lid **432** and the assembled hermetic package base **400** is hermetically sealed following block **840**. A

13

moisture getter **444** may be applied to the interior of the hermetic package lid **432**. In a preferred embodiment, the moisture getter **444** is uniformly applied with a thickness of three or more microns to the interior surface of the hermetic package lid **432** using a deposition process. Flow proceeds to block **840**.

At block **840**, the assembled hermetic package base **400** and hermetic package lid **432** are placed into the vacuum baking apparatus and second vacuum baked. Unlike block **832**, where only the assembled hermetic package base **400** is first vacuum baked, block **840** requires the hermetic package lid **432** to be placed on the assembled hermetic package base **400** prior to initiating the second vacuum bake process. The second vacuum bake process is illustrated in FIG. 12 of application Ser. No. 13/623,603. Flow proceeds to block **844**.

At block **844**, a vacuum pump in the vacuum baking apparatus is turned off. Turning the vacuum pump off prevents gases from being evacuated from the vacuum baking apparatus, and is required in order for noble gas **448** injected in block **848** to remain in the packaged hermetic integrated circuit **452** after the hermetic package lid **432** is sealed to the assembled hermetic package base **400**. Flow proceeds to block **848**.

At block **848**, a noble gas **448** is injected into the packaged hermetic integrated circuit **452**, while the packaged hermetic integrated circuit **452** is in the vacuum baking apparatus, and immediately following the second vacuum bake process. In a preferred embodiment, the noble gas **448** is Argon, and the noble gas **448** is injected into the cavity **416** to a pressure of between 0.1 to 2 Atmospheres (ATM), preferably 1 ATM, at a temperature between 200° C. and 275° C., preferably 255° C. Flow proceeds to block **852**.

At block **852**, the packaged hermetic integrated circuit **452** is hermetically and/or electrically tested. Hermetic testing is generally performed according to MIL-STD-883J. Electrical testing includes either continuity tests or functional tests, or both. If the packaged hermetic integrated circuit **452** has passed the hermeticity and electrical tests and the package leads **424** are properly trimmed to the appropriate length, the packaged hermetic integrated circuit **452** is marked and is a complete hermetic integrated circuit **452** ready for use. Flow ends at block **852**.

Referring now to FIG. 8B, a flowchart illustrating an assembly method for a hermetic packaged integrated circuit **452** in accordance with a fourth embodiment of the present invention is shown. Flow begins at block **804**.

At block **856**, an extracted die **100** is removed from from previous packaged integrated circuit. The extracted die **100** will have at least one original ball bond **112** and one original bond wire **116**. It is possible that some or all existing original bond wires **115** will be removed during the die extraction process. Flow proceeds to block **860**.

At block **860**, original bond wires **116** are removed from original ball bonds **112** of extracted die **100**. Flow proceeds to block **864**.

At block **864**, the original bond pads **104**, **108** are conditioned and/or reconditioned. Conditioning includes removing any impurities from original bond pads **104**, **108** and reconditioning applies an ENEPIG surface treatment in order to prepare the original bond pads **104**, **108** to accept new ball bonds **236** and new bond wires **240**. Instead of reconditioning, the original bond pads **104**, **108** may be cleaned and/or lapped with all metallic and chemical residues removed. Flow proceeds to block **868**.

14

At block **868**, the extracted die **100** is bonded to the interposer **404** to create a remapped extracted die **608**. Flow proceeds to block **872**.

At block **872**, a low-halide content die attach adhesive **412** is applied to the package base cavity **416**. Flow proceeds to block **876**.

At block **876**, the remapped extracted die **608** is placed into the package base cavity **416** to secure the remapped extracted die **608** to the new package base **408**. As an alternative to blocks **868-876**, the interposer **404** may first be bonded to the new package base **408**, then the extracted die **100** may be bonded to the interposer **404**. Flow proceeds to blocks **880** and **884**.

At block **880**, new bond wires **240** are provided between original bond pads **104**, **108**, conditioned original bond pads, or reconditioned bond pads **232** of the extracted die **100** and the first set of bond pads **504** of the interposer **404**. Flow proceeds to block **886**.

At block **884**, new bond wires **240** are provided between the second bond pads **508** of the interposer **404** and package leads **424** or downbonds, as required. It should be noted that steps **880** and **884** may be completed in any order, depending on what new bond wire **240** installation produces the most efficient and reliable process. Flow proceeds to block **886**.

At block **886**, the assembled hermetic package base **400** is first vacuum baked. The assembled hermetic package base **400** includes the hermetic new package base **408**, package leads **424**, remapped extracted die **608**, the die attach adhesive **412**, and new bond wires **240**. The process of first vacuum baking is illustrated in FIG. 11 of application Ser. No. 13/623,603. Flow proceeds to block **888**.

At block **888**, the assembled hermetic package base **400** is removed from the vacuum baking apparatus and the hermetic package lid **432** is placed on the assembled hermetic package base **400**. The hermetic package lid **432** is placed in proper orientation such that the combination of the hermetic package lid **432** and the assembled hermetic package base **400** is hermetically sealed following block **840**. In some embodiments, a moisture getter **444** is applied to the interior of the hermetic package lid **432**. In a preferred embodiment, the moisture getter **444** is uniformly applied with a thickness of three or more microns to the interior surface of the hermetic package lid **432** using a deposition process. Flow proceeds to block **890**.

At block **890**, the assembled hermetic package base **400** and hermetic package lid **432** are placed into the vacuum baking apparatus and second vacuum baked. Unlike block **832**, where only the assembled hermetic package base **400** is first vacuum baked, block **840** requires the hermetic package lid **432** to be placed on the assembled hermetic package base **400** prior to initiating the second vacuum bake process. The second vacuum bake process is illustrated in FIG. 12 of application Ser. No. 13/623,603. Flow proceeds to block **892**.

At block **892**, a vacuum pump in the vacuum baking apparatus is turned off. Turning the vacuum pump off prevents gases from being evacuated from the vacuum baking apparatus, and is required in order for noble gas **448** injected in block **848** to remain in the packaged hermetic integrated circuit **452** after the hermetic package lid **432** is sealed to the assembled hermetic package base **400**. Flow proceeds to block **894**.

At block **894**, a noble gas **448** is injected into the packaged hermetic integrated circuit **452**, while the packaged hermetic integrated circuit **452** is in the vacuum baking apparatus, and immediately following the second vacuum bake process. In a preferred embodiment, the noble gas **448**

15

is Argon, and the noble gas **448** is injected into the cavity **416** to a pressure of between 0.1 to 2 Atmospheres (ATM), preferably 1 ATM, at a temperature between 200° C. and 275° C., preferably 255° C. Flow proceeds to block **896**.

At block **896**, the packaged hermetic integrated circuit **452** is hermetically and/or electrically tested. Hermetic testing is generally performed according to MIL-STD-883J. Electrical testing includes either continuity tests or functional tests, or both. If the packaged hermetic integrated circuit **452** has passed the hermeticity and electrical tests and the package leads **424** are properly trimmed to the appropriate length, the packaged hermetic integrated circuit **452** is marked and is a complete hermetic integrated circuit **452** ready for use. Flow ends at block **896**.

Finally, those skilled in the art should appreciate that they can readily use the disclosed conception and specific embodiments as a basis for designing or modifying other structures for carrying out the same purposes of the present invention without departing from the spirit and scope of the invention as defined by the appended claims.

I claim:

1. A method for remapping an extracted die, comprising: removing an extracted die from a previous integrated circuit package, the extracted die comprising a plurality of original bond pads having locations that do not correspond to desired pin assignments of a new package base; and bonding an interposer to the extracted die, the interposer comprising: first bond pads configured to receive new bond wires from the plurality of original bond pads; and second bond pads corresponding to desired pin assignments of the new package base, each individually electrically coupled to one of the first bond pads and configured to receive new bond wires from package leads or downbonds of the new package base.
2. The method of claim 1, wherein original bond pad locations that do not correspond to desired pin assignments of the new package base comprises original bond pad locations for new bond wires that cross other new bond wires if the extracted die is bonded to the new package base without the interposer.
3. The method of claim 1, wherein pin assignments of the previous integrated circuit package is different than pin assignments of the new package base.
4. A method for creating a packaged integrated circuit, comprising: removing an extracted die comprising original bond pads from a previous packaged integrated circuit; removing one or more original bond wires from the extracted die; bonding the extracted die to an interposer comprising first bond pads electrically coupled to second bond pads; bonding the interposer to a new package base comprising package leads; providing new bond wires between original bond pads and first bond pads; providing new bond wires between second bond pads and package leads or downbonds; and sealing a package lid to the new package base.
5. The method of claim 4, wherein the extracted die is bonded to the interposer and the interposer is bonded to the new package base with a die attach adhesive.
6. The method of claim 4, wherein the interposer translates bond pad positions on the extracted die into second bond pad positions corresponding to pin assignments on the new package base.

16

7. The method of claim 6, wherein the interposer allows new bond wires to avoid crossing each other.

8. The method of claim 4, wherein providing new bond wires between the extracted die and the interposer comprises providing at least one new bond wire between an original ball bond of the extracted die and a first bond pad.

9. The method of claim 8, wherein the original ball bond was on an original bond pad within the previous packaged integrated circuit.

10. The method of claim 4, further comprising: after removing the one or more original bond wires: removing one or more original ball bonds from the extracted die; and removing one or more of residues and oxides on the one or more original bond pads.

11. The method of claim 10, wherein in response to removing one or more of residues and oxides, the method comprising:

reconditioning one or more bond pads on the extracted die.

12. The method of claim 11, wherein preconditioning one or more bond pads on the extracted die comprises: applying Nickel, Palladium, and Gold layers to the one or more original bond pads.

13. A method for assembling a new packaged integrated circuit, comprising:

removing an extracted die from a previous packaged integrated circuit;

bonding an interposer comprising first bond pads electrically coupled to second bond pads to the extracted die; securing the extracted die bonded to the interposer within a cavity of a new package base;

providing new bond wires between the extracted die and first bond pads and between second bond pads and package leads or downbonds of the new package base; and

sealing a package lid to the new package base.

14. The method of claim 13, wherein second bond pad locations allow new bond wires to not cross other new bond wires between the second bond pads and package leads or downbonds of the new package base.

15. The method of claim 13, the extracted die comprising: original bond pads; and

one or more original ball bonds on the original bond pads, wherein one or more original bond wires are removed from the one or more original ball bonds prior to bonding the extracted die to the interposer.

16. The method of claim 15, wherein providing new bond wires between the extracted die and first bond pads comprises providing new bond wires between the one or more original ball bonds and the first bond pads.

17. The method of claim 15, wherein after removing the original bond wires from the extracted die, the method further comprising:

removing the one or more original ball bonds from the original bond pads; and

removing one or more of residues and oxides from original bond pads that previously had original ball bonds, the bond pads having removed one or more of residues and oxides being conditioned original bond pads.

18. The method of claim 17, wherein after removing one or more of residues and oxides, the method further comprising:

reconditioning at least one conditioned original bond pad, wherein preconditioning at least one original bond pad comprises applying a Nickel layer over the conditioned

original bond pads, a Palladium layer over the Nickel layer, and a Gold layer covering the Palladium layer, wherein the reconditioned bond pads are ready to accept new bond wires and new ball bonds.

19. The method of claim 18, wherein providing new bond wires between the extracted die and first bond pads comprises providing new bond wires between the reconditioned bond pads and the first bond pads. 5

20. The method of claim 13, wherein the new packaged integrated circuit is a hermetic packaged integrated circuit comprising: 10

- a new hermetic package base;
- a hermetic package lid;
- and at least one of:
 - a low-halide die attach adhesive;
 - an inert noble gas; and
 - a moisture getter.

15

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